



LM10 Operational Amplifier and Voltage Reference

1 Features

- Input Offset Voltage: 2 mV (Maximum)
- Input Offset Current: 0.7 nA (Maximum)
- Input Bias Current: 20 nA (Maximum)
- Reference Regulation: 0.1% (Maximum)
- Offset Voltage Drift: 2 $\mu\text{V}/^\circ\text{C}$
- Reference Drift: 0.002%/°C

2 Applications

- Remote Amplifiers
- Battery-Level Indicators
- Thermocouple Transmitters
- Voltage and Current regulators

3 Description

The LM10 series are monolithic linear ICs consisting of a precision reference, an adjustable reference buffer and an independent, high-quality operational amplifier.

The unit can operate from a total supply voltage as low as 1.1 V or as high as 40 V, drawing only 270 μA . A complementary output stage swings within 15 mV of the supply terminals or will deliver $\pm 20\text{-mA}$ output current with $\pm 0.4\text{-V}$ saturation. Reference output can be as low as 200 mV.

The circuit is recommended for portable equipment and is completely specified for operation from a single power cell. In contrast, high output-drive capability, both voltage and current, along with thermal overload protection, suggest it in demanding general-purpose applications.

The device is capable of operating in a floating mode, independent of fixed supplies. It can function as a remote comparator, signal conditioner, SCR controller or transmitter for analog signals, delivering the processed signal on the same line used to supply power. It is also suited for operation in a wide range of voltage and current regulator applications, from low voltages to several hundred volts, providing greater precision than existing ICs.

This series is available in the three standard temperature ranges, with the commercial part having relaxed limits. In addition, a low-voltage specification (suffix L) is available in the limited temperature ranges at a cost savings.

Device Information⁽¹⁾

PART NUMBER	PACKAGE	BODY SIZE (NOM)
LM10	SOIC (14)	8.992 mm × 7.498 mm
	SDIP (8)	8.255 mm × 8.255 mm
	PDIP (8)	9.81 mm × 6.35 mm

(1) For all available packages, see the orderable addendum at the end of the data sheet.

Operational Amplifier Schematic

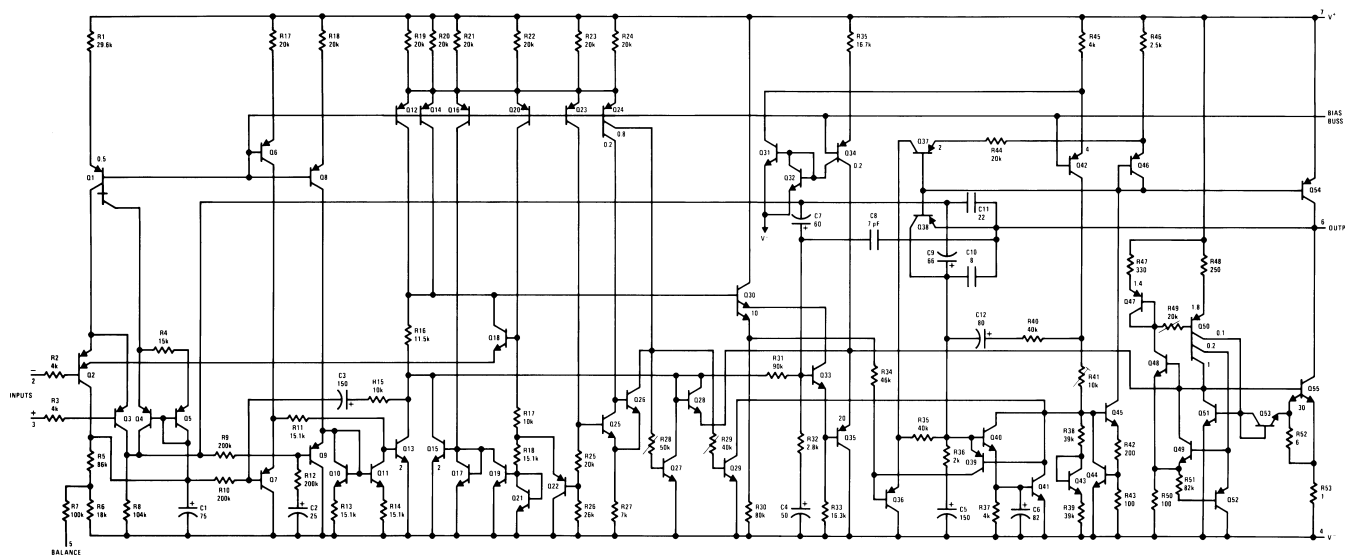


Table of Contents

1 Features	1	7.4 Device Functional Modes.....	17
2 Applications	1	8 Application and Implementation	18
3 Description	1	8.1 Application Information.....	18
4 Revision History	2	8.2 Typical Application	18
5 Pin Configuration and Functions	3	8.3 System Examples	19
6 Specifications	4	9 Power Supply Recommendations	27
6.1 Absolute Maximum Ratings	4	10 Layout	27
6.2 Recommended Operating Conditions.....	4	10.1 Layout Guidelines	27
6.3 Thermal Information	4	10.2 Layout Example	27
6.4 Electrical Characteristics LM10/LM10B	5	11 Device and Documentation Support	28
6.5 Electrical Characteristics, LM10C	6	11.1 Device Support	28
6.6 Electrical Characteristics, LM10BL	8	11.2 Documentation Support	28
6.7 Electrical Characteristics, LM10CL	9	11.3 Community Resources.....	28
6.8 Typical Characteristics.....	11	11.4 Trademarks	29
7 Detailed Description	17	11.5 Electrostatic Discharge Caution.....	29
7.1 Overview	17	11.6 Glossary	29
7.2 Functional Block Diagram	17	12 Mechanical, Packaging, and Orderable Information	29
7.3 Feature Description.....	17		

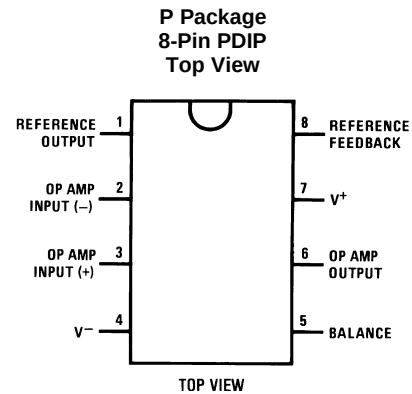
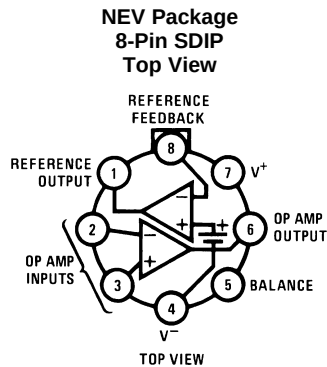
4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision D (March 2013) to Revision E	Page
Added <i>Pin Configuration and Functions</i> section, <i>ESD Ratings</i> table, <i>Feature Description</i> section, <i>Device Functional Modes</i>, <i>Application and Implementation</i> section, <i>Power Supply Recommendations</i> section, <i>Layout</i> section, <i>Device and Documentation Support</i> section, and <i>Mechanical, Packaging, and Orderable Information</i> section	1

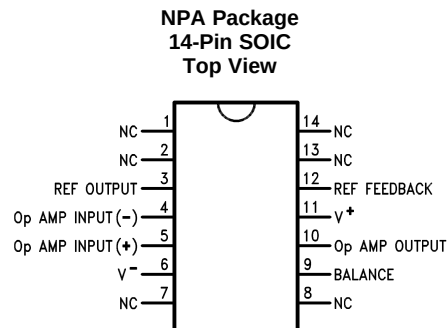
Changes from Revision C (March 2013) to Revision D	Page
Changed layout of National Data Sheet to TI format	26

5 Pin Configuration and Functions



Pin Functions — 8-Pin SDIP or PDIP

PIN		I/O	DESCRIPTION
NAME	NO.		
Balance	5	I	Used for offset nulling
Op Amp Input (+)	3	I	Noninverting input of operational amplifier
Op Amp Input (-)	2	I	Inverting input of operational amplifier
Op Amp Output	6	O	Output terminal of operational amplifier
Reference Feedback	8	I	Feedback terminal of reference
Reference Output	1	O	Output terminal of reference
V+	7	I	Positive supply voltage
V-	4	I	Negative supply voltage



Pin Functions — 14-Pin SOIC

PIN		I/O	DESCRIPTION
NAME	NO.		
Balance	9	I	Used for offset nulling
NC	1, 2, 7, 8, 14, 13	—	No connection
Op Amp Input (-)	4	I	Inverting input of operational amplifier
Op Amp Input (+)	5	I	Noninverting input of operational amplifier
Op Amp Output	10	O	Output terminal of operational amplifier
Reference Feedback	12	I	Feedback terminal of reference
Reference Output	3	O	Output terminal of reference
V+	11	I	Positive supply voltage
V-	6	I	Negative supply voltage

6 Specifications

6.1 Absolute Maximum Ratings

 See ⁽¹⁾⁽²⁾⁽³⁾

			MIN	MAX	UNIT
Total supply voltage	LM10/LM10B/LM10C		45		V
	LM10BL/LM10CL		7		V
Differential input voltage ⁽⁴⁾	LM10/LM10B/LM10C		±40		V
	LM10BL/LM10CL		±7		V
Power dissipation ⁽⁵⁾			Internally limited		
Output short-circuit duration ⁽⁶⁾			Continuous		
Lead temperature	TO	Soldering (10 seconds)	300		°C
	DIP	Soldering (10 seconds)	260		°C
		Vapor phase (60 seconds)	215		°C
		Infrared (15 seconds)	220		°C
Maximum junction temperature	LM10		150		°C
	LM10B		100		°C
	LM10C		85		°C
Storage temperature, T _{stg}			−55	150	°C

- (1) Refer to RETS10X for LM10H military specifications.
- (2) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (3) If Military/Aerospace specified devices are required, please contact the TI Sales Office/Distributors for availability and specifications.
- (4) The Input voltage can exceed the supply voltages provided that the voltage from the input to any other terminal does not exceed the maximum differential input voltage and excess dissipation is accounted for when $V_{IN} < V^-$.
- (5) The maximum, operating-junction temperature is 150°C for the LM10, 100°C for the LM10B(L) and 85°C for the LM10C(L). At elevated temperatures, devices must be derated based on package thermal resistance.
- (6) Internal thermal limiting prevents excessive heating that could result in sudden failure, but the IC can be subjected to accelerated stress with a shorted output and worst-case conditions.

6.2 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
V _S	Supply input voltage range (V ⁻) – (V ⁺)	1.2		40	V
V _{CM}	Common-mode voltage	(V ⁻)		(V ⁺) – 0.85	V
V _{REF}	Reference voltage		0.2		V
I _{REF}	Reference current	0		1	mA

6.3 Thermal Information

THERMAL METRIC ⁽¹⁾		LM10			UNIT
		NEV (SDIP)	NPA (SOIC)	P (PDIP)	
		8 PINS	14 PINS	8 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	150	90	87	°C/W
R _{θJC(top)}	Junction-to-case (top) thermal resistance	45	—	—	°C/W

- (1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report, [SPRA953](#).

6.4 Electrical Characteristics LM10/LM10B

 $T_J = 25^\circ\text{C}$ unless otherwise specified⁽¹⁾

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Input offset voltage	$T_J = 25^\circ\text{C}$		0.3	2	mV
	$T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$ (see ⁽¹⁾)			3	mV
Input offset current ⁽²⁾	$T_J = 25^\circ\text{C}$		0.25	0.7	nA
	$T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$ (see ⁽¹⁾)			1.5	nA
Input bias current	$T_J = 25^\circ\text{C}$		10	20	nA
	$T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$ (see ⁽¹⁾)			30	nA
Input resistance	$T_J = 25^\circ\text{C}$	250	500		k Ω
	$T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$ (see ⁽¹⁾)	150			k Ω
Large signal voltage gain	$V_S = \pm 20\text{ V}$, $I_{\text{OUT}} = 0$	120	400		V/mV
	$V_{\text{OUT}} = \pm 19.95\text{ V}$, $T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$ (see ⁽¹⁾)	80			V/mV
	$V_S = \pm 20\text{ V}$, $V_{\text{OUT}} = \pm 19.4\text{ V}$	50	130		V/mV
	$I_{\text{OUT}} = \pm 20\text{ mA}$, $T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$ (see ⁽¹⁾)	20			V/mV
	$I_{\text{OUT}} = \pm 15\text{ mA}$, $T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$ (see ⁽¹⁾)	20			V/mV
	$V_S = \pm 0.6\text{ V}$, $I_{\text{OUT}} = \pm 2\text{ mA}$	1.5	3		V/mV
	$V_S = \pm 0.65\text{ V}$, $I_{\text{OUT}} = \pm 2\text{ mA}$, $T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$ (see ⁽¹⁾)	1.5	3		V/mV
	$V_{\text{OUT}} = \pm 0.4\text{ V}$, $T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$ (see ⁽¹⁾)	0.5			V/mV
	$V_{\text{OUT}} = \pm 0.3\text{ V}$, $V_{\text{CM}} = -0.4\text{ V}$, $T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$ (see ⁽¹⁾)	0.5			V/mV
Shunt gain ⁽³⁾	$1.2\text{ V} \leq V_{\text{OUT}} \leq 40\text{ V}$, $R_L = 1.1\text{ k}\Omega$	14	33		V/mV
	$1.3\text{ V} \leq V_{\text{OUT}} \leq 40\text{ V}$, $R_L = 1.1\text{ k}\Omega$, $T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$ (see ⁽¹⁾)	14	33		V/mV
	$0.1\text{ mA} \leq I_{\text{OUT}} \leq 5\text{ mA}$, $T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$ (see ⁽¹⁾)	6			V/mV
	$1.5\text{ V} \leq V^+ \leq 40\text{ V}$, $R_L = 250\text{ }\Omega$	8	25		V/mV
	$0.1\text{ mA} \leq I_{\text{OUT}} \leq 20\text{ mA}$, $T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$ (see ⁽¹⁾)	4			V/mV
Common-mode rejection	$-20\text{ V} \leq V_{\text{CM}} \leq 19.15\text{ V}$	93	102		dB
	$-20\text{ V} \leq V_{\text{CM}} \leq 19\text{ V}$, $T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$ (see ⁽¹⁾)	93	102		dB
	$V_S = \pm 20\text{ V}$, $T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$ (see ⁽¹⁾)	87			dB
Supply-voltage rejection	$-0.2\text{ V} \geq V^- \geq -39\text{ V}$	90	96		dB
	$V^+ = 1\text{ V}$, $T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$ (see ⁽¹⁾)	84			dB
	$V^+ = 1.1\text{ V}$, $T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$ (see ⁽¹⁾)	84			dB
	$1\text{ V} \leq V^+ \leq 39.8\text{ V}$	96	106		dB
	$1.1\text{ V} \leq V^+ \leq 39.8\text{ V}$, $T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$ (see ⁽¹⁾)	96	106		dB
	$V^- = -0.2\text{ V}$, $T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$ (see ⁽¹⁾)	90			dB
Offset voltage drift			2		$\mu\text{V}/^\circ\text{C}$
Offset current drift			2		$\text{pA}/^\circ\text{C}$
Bias current drift	$T_C < 100^\circ\text{C}$		60		$\text{pA}/^\circ\text{C}$
Line regulation	$1.2\text{ V} \leq V_S \leq 40\text{ V}$		0.001	0.003	%/V
	$1.3\text{ V} \leq V_S \leq 40\text{ V}$, $T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$ (see ⁽¹⁾)		0.001	0.003	%/V
	$0 \leq I_{\text{REF}} \leq 1\text{ mA}$, $V_{\text{REF}} = 200\text{ mV}$, $T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$ (see ⁽¹⁾)			0.006	%/V
Load regulation	$0 \leq I_{\text{REF}} \leq 1\text{ mA}$		0.01%	0.1%	
	$V^+ - V_{\text{REF}} \geq 1\text{ V}$, $T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$ (see ⁽¹⁾)			0.15%	
	$V^+ - V_{\text{REF}} \geq 1.1\text{ V}$, $T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$ (see ⁽¹⁾)			0.15%	

(1) These specifications apply for $V^- \leq V_{\text{CM}} \leq V^+ - 0.85\text{ V}$, 1 V ($T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$), 1.2 V , 1.3 V ($T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$) $< V_S \leq V_{\text{MAX}}$, $V_{\text{REF}} = 0.2\text{ V}$ and $0 \leq I_{\text{REF}} \leq 1\text{ mA}$, unless otherwise specified: $V_{\text{MAX}} = 40\text{ V}$ for the standard part and 6.5 V for the low voltage part. The full-temperature-range operation is -55°C to 125°C for the LM10, -25°C to 85°C for the LM10B(L) and 0°C to 70°C for the LM10C(L). The specifications do not include the effects of thermal gradients ($\tau_1 \approx 20\text{ ms}$), die heating ($\tau_2 \approx 0.2\text{ s}$) or package heating. Gradient effects are small and tend to offset the electrical error (see curves).

(2) For $T_J > 90^\circ\text{C}$, I_{OS} may exceed 1.5 nA for $V_{\text{CM}} = V^-$. With $T_J = 125^\circ\text{C}$ and $V^- \leq V_{\text{CM}} \leq V^+ + 0.1\text{ V}$, $I_{\text{OS}} \leq 5\text{ nA}$.

(3) This defines operation in floating applications such as the bootstrapped regulator or two-wire transmitter. Output is connected to the V^+ terminal of the IC and input common mode is referred to V^- (see [System Examples](#)). Effect of larger output-voltage swings with higher load resistance can be accounted for by adding the positive-supply rejection error.

Electrical Characteristics LM10/LM10B (continued)

 $T_J = 25^\circ\text{C}$ unless otherwise specified⁽¹⁾

PARAMETER	TEST CONDITIONS		MIN	TYP	MAX	UNIT
Amplifier gain	0.2 V ≤ V _{REF} ≤ 35 V	T _J =25°C	50	75		V/mV
		T _{MIN} ≤ T _J ≤ T _{MAX} (see ⁽¹⁾)	23			V/mV
Feedback sense voltage	T _J =25°C		195	200	205	mV
	T _{MIN} ≤ T _J ≤ T _{MAX} (see ⁽¹⁾)		194		206	mV
Feedback current	T _J =25°C			20	50	nA
	T _{MIN} ≤ T _J ≤ T _{MAX} (see ⁽¹⁾)				65	nA
Reference drift				0.002		%/°C
Supply current	T _J =25°C			270	400	μA
	T _{MIN} ≤ T _J ≤ T _{MAX} (see ⁽¹⁾)				500	μA
Supply current change	1.2 V ≤ V _S ≤ 40 V	T _J =25°C		15		μA
		T _{MIN} ≤ T _J ≤ T _{MAX} (see ⁽¹⁾)			75	
	1.3 V ≤ V _S ≤ 40 V	T _J =25°C		15		μA
		T _{MIN} ≤ T _J ≤ T _{MAX} (see ⁽¹⁾)			75	

6.5 Electrical Characteristics, LM10C

 $T_J = 25^\circ\text{C}$ unless otherwise specified⁽¹⁾

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Input offset voltage	$T_J = 25^\circ\text{C}$		0.5	4	mV
	$T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$ (see ⁽¹⁾)			5	mV
Input offset current ⁽²⁾	$T_J = 25^\circ\text{C}$		0.4	2	nA
	$T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$ (see ⁽¹⁾)			3	nA
Input bias current	$T_J = 25^\circ\text{C}$		12	30	nA
	$T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$ (see ⁽¹⁾)			40	nA
Input resistance	$T_J = 25^\circ\text{C}$	150	400		k Ω
	$T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$ (see ⁽¹⁾)	115			k Ω
Large signal voltage gain	$V_S = \pm 20\text{ V}$, $I_{\text{OUT}} = 0$	80	400		V/mV
	$V_{\text{OUT}} = \pm 19.95\text{ V}$, $T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$ (see ⁽¹⁾)	50			V/mV
	$V_S = \pm 20\text{ V}$, $V_{\text{OUT}} = \pm 19.4\text{ V}$	25	130		V/mV
	$I_{\text{OUT}} = \pm 20\text{ mA}$, $T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$ (see ⁽¹⁾)	15			V/mV
	$I_{\text{OUT}} = \pm 15\text{ mA}$, $T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$ (see ⁽¹⁾)	15			V/mV
	$V_S = \pm 0.6\text{ V}$, $I_{\text{OUT}} = \pm 2\text{ mA}$	1	3		V/mV
	$V_S = 0.65\text{ V}$, $I_{\text{OUT}} = \pm 2\text{ mA}$, $T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$ (see ⁽¹⁾)	1	3		V/mV
	$V_{\text{OUT}} = \pm 0.4\text{ V}$, $T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$ (see ⁽¹⁾)	0.75			V/mV
Shunt gain ⁽³⁾	$V_{\text{OUT}} = \pm 0.3\text{ V}$, $V_{\text{CM}} = -0.4\text{ V}$, $T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$ (see ⁽¹⁾)	0.75			V/mV
	$1.2\text{ V} \leq V_{\text{OUT}} \leq 40\text{ V}$, $R_L = 1.1\text{ k}\Omega$	10	33		V/mV
	$1.3\text{ V} \leq V_{\text{OUT}} \leq 40\text{ V}$, $R_L = 1.1\text{ k}\Omega$, $T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$ (see ⁽¹⁾)	10	33		V/mV
	$0.1\text{ mA} \leq I_{\text{OUT}} \leq 5\text{ mA}$, $T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$ (see ⁽¹⁾)	6			V/mV
	$1.5\text{ V} \leq V^+ \leq 40\text{ V}$, $R_L = 250\text{ }\Omega$	6	25		V/mV
	$0.1\text{ mA} \leq I_{\text{OUT}} \leq 20\text{ mA}$, $T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$ (see ⁽¹⁾)	4			V/mV

- (1) These specifications apply for $V^- \leq V_{\text{CM}} \leq V^+ - 0.85\text{ V}$, 1 V ($T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$), 1.2 V , 1.3 V ($T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$) $< V_S \leq V_{\text{MAX}}$, $V_{\text{REF}} = 0.2\text{ V}$ and $0 \leq I_{\text{REF}} \leq 1\text{ mA}$, unless otherwise specified: $V_{\text{MAX}} = 40\text{ V}$ for the standard part and 6.5 V for the low voltage part. The full-temperature-range operation is -55°C to 125°C for the LM10, -25°C to 85°C for the LM10B(L) and 0°C to 70°C for the LM10C(L). The specifications do not include the effects of thermal gradients ($\tau_1 \approx 20\text{ ms}$), die heating ($\tau_2 \approx 0.2\text{ s}$) or package heating. Gradient effects are small and tend to offset the electrical error (see curves).
- (2) For $T_J > 90^\circ\text{C}$, I_{OS} may exceed 1.5 nA for $V_{\text{CM}} = V^-$. With $T_J = 125^\circ\text{C}$ and $V^- \leq V_{\text{CM}} \leq V^+ + 0.1\text{ V}$, $I_{\text{OS}} \leq 5\text{ nA}$.
- (3) This defines operation in floating applications such as the bootstrapped regulator or two-wire transmitter. Output is connected to the V^+ terminal of the IC and input common mode is referred to V^- (see [System Examples](#)). Effect of larger output-voltage swings with higher load resistance can be accounted for by adding the positive-supply rejection error.

Electrical Characteristics, LM10C (continued)

 $T_J = 25^\circ\text{C}$ unless otherwise specified⁽¹⁾

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Common-mode rejection	$-20\text{ V} \leq V_{CM} \leq 19.15\text{ V}$	90	102		dB
	$-20\text{ V} \leq V_{CM} \leq 19\text{ V}$	90	102		dB
	$V_S = \pm 20\text{ V}$, $T_{MIN} \leq T_J \leq T_{MAX}$ (see ⁽¹⁾)	87			dB
Supply-voltage rejection	$-0.2\text{ V} \geq V^- \geq -39\text{ V}$	87	96		dB
	$V^+ = 1\text{ V}$, $T_{MIN} \leq T_J \leq T_{MAX}$ (see ⁽¹⁾)	84			dB
	$V^+ = 1.1\text{ V}$, $T_{MIN} \leq T_J \leq T_{MAX}$ (see ⁽¹⁾)	84			dB
	$1\text{ V} \leq V^+ \leq 39.8\text{ V}$	93	106		dB
	$1.1\text{ V} \leq V^+ \leq 39.8\text{ V}$, $T_{MIN} \leq T_J \leq T_{MAX}$ (see ⁽¹⁾)	93	106		dB
	$V^- = -0.2\text{ V}$, $T_{MIN} \leq T_J \leq T_{MAX}$ (see ⁽¹⁾)	90			dB
Offset voltage drift			5		$\mu\text{V}/^\circ\text{C}$
Offset current drift			5		$\text{pA}/^\circ\text{C}$
Bias current drift	$T_C < 100^\circ\text{C}$		90		$\text{pA}/^\circ\text{C}$
Line regulation	$1.2\text{ V} \leq V_S \leq 40\text{ V}$		0.001	0.008	%/V
	$1.3\text{ V} \leq V_S \leq 40\text{ V}$, $T_{MIN} \leq T_J \leq T_{MAX}$ (see ⁽¹⁾)		0.001	0.008	%/V
	$0 \leq I_{REF} \leq 1\text{ mA}$, $V_{REF} = 200\text{ mV}$, $T_{MIN} \leq T_J \leq T_{MAX}$ (see ⁽¹⁾)			0.01	%/V
Load regulation	$0 \leq I_{REF} \leq 1\text{ mA}$		0.01%	0.15%	
	$V^+ - V_{REF} \geq 1\text{ V}$, $T_{MIN} \leq T_J \leq T_{MAX}$ (see ⁽¹⁾)			0.2%	
	$V^+ - V_{REF} \geq 1.1\text{ V}$, $T_{MIN} \leq T_J \leq T_{MAX}$ (see ⁽¹⁾)			0.2%	
Amplifier gain	$0.2\text{ V} \leq V_{REF} \leq 35\text{ V}$	$T_J = 25^\circ\text{C}$	25	70	V/mV
		$T_{MIN} \leq T_J \leq T_{MAX}$ (see ⁽¹⁾)	15		V/mV
Feedback sense voltage	$T_J = 25^\circ\text{C}$	190	200	210	mV
	$T_{MIN} \leq T_J \leq T_{MAX}$ (see ⁽¹⁾)	189		211	mV
Feedback current	$T_J = 25^\circ\text{C}$		22	75	nA
	$T_{MIN} \leq T_J \leq T_{MAX}$ (see ⁽¹⁾)			90	nA
Reference drift			0.003		%/°C
Supply current	$T_J = 25^\circ\text{C}$		300	500	μA
	$T_{MIN} \leq T_J \leq T_{MAX}$ (see ⁽¹⁾)			570	μA
Supply current change	$1.2\text{ V} \leq V_S \leq 40\text{ V}$	$T_J = 25^\circ\text{C}$	15		μA
		$T_{MIN} \leq T_J \leq T_{MAX}$ (see ⁽¹⁾)		75	
	$1.3\text{ V} \leq V_S \leq 40\text{ V}$	$T_J = 25^\circ\text{C}$	15		μA
		$T_{MIN} \leq T_J \leq T_{MAX}$ (see ⁽¹⁾)		75	

6.6 Electrical Characteristics, LM10BL

 $T_J = 25^\circ\text{C}$ unless otherwise specified. ⁽¹⁾

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Input offset voltage	$T_J = 25^\circ\text{C}$		0.3	2	mV
	$T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$ (see ⁽¹⁾)			3	mV
Input offset current ⁽²⁾	$T_J = 25^\circ\text{C}$		0.1	0.7	nA
	$T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$ (see ⁽¹⁾)			1.5	nA
Input bias current	$T_J = 25^\circ\text{C}$		10	20	nA
	$T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$ (see ⁽¹⁾)			30	nA
Input resistance	$T_J = 25^\circ\text{C}$	250	500		k Ω
	$T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$ (see ⁽¹⁾)	150			k Ω
Large signal voltage gain	$V_S = \pm 3.25\text{ V}$, $I_{\text{OUT}} = 0$	60	300		V/mV
	$V_{\text{OUT}} = \pm 3.2\text{ V}$, $T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$ (see ⁽¹⁾)	40			V/mV
	$V_S = \pm 3.25\text{ V}$, $I_{\text{OUT}} = 10\text{ mA}$	10	25		V/mV
	$V_{\text{OUT}} = \pm 2.75\text{ V}$, $T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$ (see ⁽¹⁾)	4			V/mV
	$V_S = \pm 0.6\text{ V}$, $I_{\text{OUT}} = \pm 2\text{ mA}$	1.5	3		V/mV
	$V_S = 0.65\text{ V}$, $I_{\text{OUT}} = \pm 2\text{ mA}$, $T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$ (see ⁽¹⁾)	1.5	3		V/mV
	$V_{\text{OUT}} = \pm 0.4\text{ V}$, $V_{\text{CM}} = -0.4\text{ V}$, $T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$ (see ⁽¹⁾)	0.5			V/mV
	$V_{\text{OUT}} = \pm 0.3\text{ V}$, $V_{\text{CM}} = -0.4\text{ V}$, $T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$ (see ⁽¹⁾)	0.5			V/mV
Shunt gain ⁽³⁾	$1.5\text{ V} \leq V^+ \leq 6.5\text{ V}$, $R_L = 500\ \Omega$	8	30		V/mV
	$0.1\text{ mA} \leq I_{\text{OUT}} \leq 10\text{ mA}$, $T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$ (see ⁽¹⁾)	4			V/mV
Common-mode rejection	$-3.25\text{ V} \leq V_{\text{CM}} \leq 2.4\text{ V}$	89	102		dB
	$-3.25\text{ V} \leq V_{\text{CM}} \leq 2.25\text{ V}$, $T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$ (see ⁽¹⁾)				
	$V_S = \pm 3.25\text{ V}$, $T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$ (see ⁽¹⁾)	83			dB
Supply-voltage rejection	$-0.2\text{ V} \geq V^- \geq -5.4\text{ V}$	86	96		dB
	$V^+ = 1\text{ V}$, $T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$ (see ⁽¹⁾)	80			dB
	$V^+ = 1.2\text{ V}$, $T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$ (see ⁽¹⁾)	80			dB
	$1\text{ V} \leq V^+ \leq 6.3\text{ V}$	94	106		dB
	$1.1\text{ V} \leq V^+ \leq 6.3\text{ V}$, $T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$ (see ⁽¹⁾)	94	106		dB
	$V^- = 0.2\text{ V}$, $T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$ (see ⁽¹⁾)	88			dB
Offset voltage drift			2		$\mu\text{V}/^\circ\text{C}$
Offset current drift			2		$\text{pA}/^\circ\text{C}$
Bias current drift			60		$\text{pA}/^\circ\text{C}$
Line regulation	$1.2\text{ V} \leq V_S \leq 6.5\text{ V}$		0.001	0.01	%/V
	$1.3\text{ V} \leq V_S \leq 6.5\text{ V}$, $T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$ (see ⁽¹⁾)		0.001	0.01	%/V
	$0 \leq I_{\text{REF}} \leq 0.5\text{ mA}$, $V_{\text{REF}} = 200\text{ mV}$, $T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$ (see ⁽¹⁾)			0.02	%/V
Load regulation	$0 \leq I_{\text{REF}} \leq 0.5\text{ mA}$		0.01%	0.1%	
	$V^+ - V_{\text{REF}} \geq 1\text{ V}$, $T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$ (see ⁽¹⁾)			0.15%	
	$V^+ - V_{\text{REF}} \geq 1.1\text{ V}$, $T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$ (see ⁽¹⁾)			0.15%	
Amplifier gain	$0.2\text{ V} \leq V_{\text{REF}} \leq 5.5\text{ V}$	$T_J = 25^\circ\text{C}$	30	70	V/mV
		$T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$ (see ⁽¹⁾)	20		V/mV
Feedback sense voltage	$T_J = 25^\circ\text{C}$	195	200	205	mV
	$T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$ (see ⁽¹⁾)	194		206	mV

- (1) These specifications apply for $V^- \leq V_{\text{CM}} \leq V^+ - 0.85\text{ V}$, 1 V ($T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$), 1.2 V , 1.3 V ($T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$) $< V_S \leq V_{\text{MAX}}$, $V_{\text{REF}} = 0.2\text{ V}$ and $0 \leq I_{\text{REF}} \leq 1\text{ mA}$, unless otherwise specified: $V_{\text{MAX}} = 40\text{ V}$ for the standard part and 6.5 V for the low voltage part. The full-temperature-range operation is -55°C to 125°C for the LM10, -25°C to 85°C for the LM10B(L) and 0°C to 70°C for the LM10C(L). The specifications do not include the effects of thermal gradients ($\tau_1 \approx 20\text{ ms}$), die heating ($\tau_2 \approx 0.2\text{ s}$) or package heating. Gradient effects are small and tend to offset the electrical error (see curves).

- (2) For $T_J > 90^\circ\text{C}$, I_{OS} may exceed 1.5 nA for $V_{\text{CM}} = V^-$. With $T_J = 125^\circ\text{C}$ and $V^- \leq V_{\text{CM}} \leq V^+ + 0.1\text{ V}$, $I_{\text{OS}} \leq 5\text{ nA}$.

- (3) This defines operation in floating applications such as the bootstrapped regulator or two-wire transmitter. Output is connected to the V^+ terminal of the IC and input common mode is referred to V^- (see [System Examples](#)). Effect of larger output-voltage swings with higher load resistance can be accounted for by adding the positive-supply rejection error.

Electrical Characteristics, LM10BL (continued)

 $T_J = 25^\circ\text{C}$ unless otherwise specified. ⁽¹⁾

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Feedback current	$T_J = 25^\circ\text{C}$		20	50	nA
	$T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$ (see ⁽¹⁾)			65	nA
Reference drift			0.002		%/ $^\circ\text{C}$
Supply current	$T_J = 25^\circ\text{C}$		260	400	μA
	$T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$ (see ⁽¹⁾)			500	μA

6.7 Electrical Characteristics, LM10CL

 $T_J = 25^\circ\text{C}$ unless otherwise specified. ⁽¹⁾

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Input offset voltage	$T_J = 25^\circ\text{C}$		0.5	4	mV
	$T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$ (see ⁽¹⁾)			5	mV
Input offset current ⁽²⁾	$T_J = 25^\circ\text{C}$		0.2	2	nA
	$T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$ (see ⁽¹⁾)			3	nA
Input bias current	$T_J = 25^\circ\text{C}$		12	30	nA
	$T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$ (see ⁽¹⁾)			40	nA
Input resistance	$T_J = 25^\circ\text{C}$	150	400		k Ω
	$T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$ (see ⁽¹⁾)	115			k Ω
Large signal voltage gain	$V_S = \pm 3.25\text{ V}$, $I_{\text{OUT}} = 0$	40	300		V/mV
	$V_{\text{OUT}} = \pm 3.2\text{ V}$, $T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$ (see ⁽¹⁾)	25			V/mV
	$V_S = \pm 3.25\text{ V}$, $I_{\text{OUT}} = 10\text{ mA}$	5	25		V/mV
	$V_{\text{OUT}} = \pm 2.75\text{ V}$, $T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$ (see ⁽¹⁾)	3			V/mV
	$V_S = \pm 0.6\text{ V}$, $I_{\text{OUT}} = \pm 2\text{ mA}$	1	3		V/mV
	$V_S = 0.65\text{ V}$, $I_{\text{OUT}} = \pm 2\text{ mA}$, $T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$ (see ⁽¹⁾)	1	3		V/mV
	$V_{\text{OUT}} = \pm 0.4\text{ V}$, $V_{\text{CM}} = -0.4\text{ V}$, $T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$ (see ⁽¹⁾)	0.75			V/mV
	$V_{\text{OUT}} = \pm 0.3\text{ V}$, $V_{\text{CM}} = -0.4\text{ V}$, $T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$ (see ⁽¹⁾)	0.75			V/mV
Shunt gain ⁽³⁾	$1.5\text{ V} \leq V^+ \leq 6.5\text{ V}$, $R_L = 500\ \Omega$	6	30		V/mV
	$0.1\text{ mA} \leq I_{\text{OUT}} \leq 10\text{ mA}$, $T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$ (see ⁽¹⁾)	4			V/mV
Common-mode rejection	$-3.25\text{ V} \leq V_{\text{CM}} \leq 2.4\text{ V}$	80	102		dB
	$-3.25\text{ V} \leq V_{\text{CM}} \leq 2.25\text{ V}$, $T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$ (see ⁽¹⁾)	80	102		dB
	$V_S = \pm 3.25\text{ V}$, $T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$ (see ⁽¹⁾)	74			dB
Supply-voltage rejection	$-0.2\text{ V} \geq V^- \geq -5.4\text{ V}$	80	96		dB
	$V^+ = 1\text{ V}$, $T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$ (see ⁽¹⁾)	74			dB
	$V^+ = 1.2\text{ V}$, $T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$ (see ⁽¹⁾)	74			dB
	$1\text{ V} \leq V^+ \leq 6.3\text{ V}$	80	106		dB
	$1.1\text{ V} \leq V^+ \leq 6.3\text{ V}$, $T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$ (see ⁽¹⁾)	80	106		dB
	$V^- = 0.2\text{ V}$, $T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$ (see ⁽¹⁾)	74			dB
Offset voltage drift			5		$\mu\text{V}/^\circ\text{C}$
Offset current drift			5		$\text{pA}/^\circ\text{C}$
Bias current drift			90		$\text{pA}/^\circ\text{C}$

(1) These specifications apply for $V^- \leq V_{\text{CM}} \leq V^+ - 0.85\text{ V}$, 1 V ($T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$), 1.2 V , 1.3 V ($T_{\text{MIN}} \leq T_J \leq T_{\text{MAX}}$) $< V_S \leq V_{\text{MAX}}$, $V_{\text{REF}} = 0.2\text{ V}$ and $0 \leq I_{\text{REF}} \leq 1\text{ mA}$, unless otherwise specified: $V_{\text{MAX}} = 40\text{ V}$ for the standard part and 6.5 V for the low voltage part. The full-temperature-range operation is -55°C to 125°C for the LM10, -25°C to 85°C for the LM10B(L) and 0°C to 70°C for the LM10C(L). The specifications do not include the effects of thermal gradients ($\tau_1 \approx 20\text{ ms}$), die heating ($\tau_2 \approx 0.2\text{ s}$) or package heating. Gradient effects are small and tend to offset the electrical error (see curves).

(2) For $T_J > 90^\circ\text{C}$, I_{OS} may exceed 1.5 nA for $V_{\text{CM}} = V^-$. With $T_J = 125^\circ\text{C}$ and $V^- \leq V_{\text{CM}} \leq V^+ + 0.1\text{ V}$, $I_{\text{OS}} \leq 5\text{ nA}$.

(3) This defines operation in floating applications such as the bootstrapped regulator or two-wire transmitter. Output is connected to the V^+ terminal of the IC and input common mode is referred to V^- (see [System Examples](#)). Effect of larger output-voltage swings with higher load resistance can be accounted for by adding the positive-supply rejection error.

LM10

SNOSBH4E – MAY 1998 – REVISED OCTOBER 2015

www.ti.com
Electrical Characteristics, LM10CL (continued)
 $T_J = 25^\circ\text{C}$ unless otherwise specified.⁽¹⁾

PARAMETER	TEST CONDITIONS		MIN	TYP	MAX	UNIT
Line regulation	1.2 V ≤ V _S ≤ 6.5 V			0.001	0.02	%/V
	1.3 V ≤ V _S ≤ 6.5 V, T _{MIN} ≤ T _J ≤ T _{MAX} (see ⁽¹⁾)			0.001	0.02	%/V
	0 ≤ I _{REF} ≤ 0.5 mA, V _{REF} = 200 mV, T _{MIN} ≤ T _J ≤ T _{MAX} (see ⁽¹⁾)				0.03	%/V
Load regulation	0 ≤ I _{REF} ≤ 0.5 mA			0.01%	0.15%	
	V ⁺ − V _{REF} ≥ 1 V, T _{MIN} ≤ T _J ≤ T _{MAX} (see ⁽¹⁾)				0.2%	
	V ⁺ − V _{REF} ≥ 1.1 V, T _{MIN} ≤ T _J ≤ T _{MAX} (see ⁽¹⁾)				0.2%	
Amplifier gain	0.2 V ≤ V _{REF} ≤ 5.5 V	T _J =25°C	20	70		V/mV
		T _{MIN} ≤ T _J ≤ T _{MAX} (see ⁽¹⁾)	15			V/mV
Feedback sense voltage	T _J =25°C		190	200	210	mV
	T _{MIN} ≤ T _J ≤ T _{MAX} (see ⁽¹⁾)		189		211	mV
Feedback current	T _J =25°C			22	75	nA
	T _{MIN} ≤ T _J ≤ T _{MAX} (see ⁽¹⁾)				90	nA
Reference drift				0.003		%/°C
Supply current	T _J =25°C			280	500	μA
	T _{MIN} ≤ T _J ≤ T _{MAX} (see ⁽¹⁾)				570	μA

6.8 Typical Characteristics

6.8.1 Typical Characteristics (Op Amp)

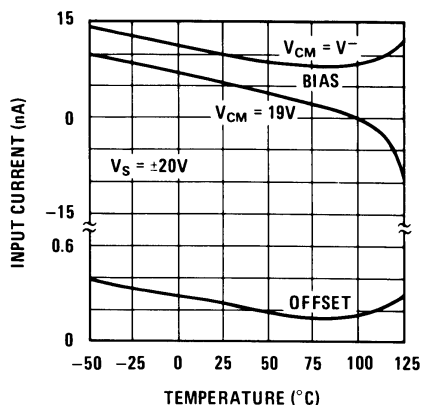


Figure 1. Input Current

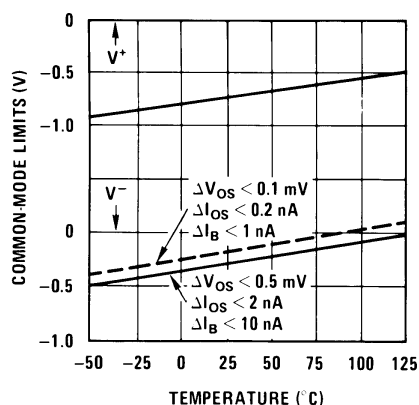


Figure 2. Common-Mode Limits

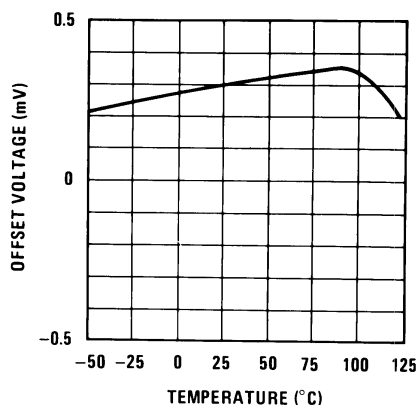


Figure 3. Output Voltage Drift

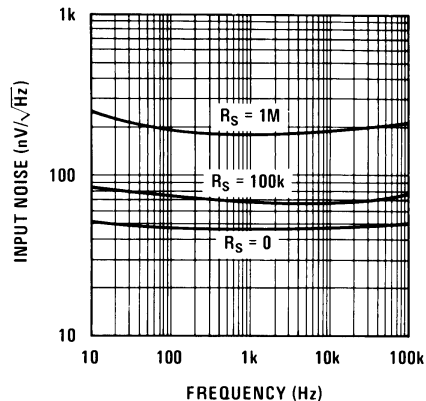


Figure 4. Input Noise Voltage

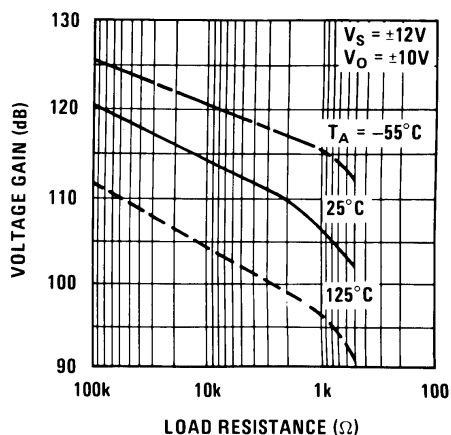


Figure 5. DC Voltage Gain

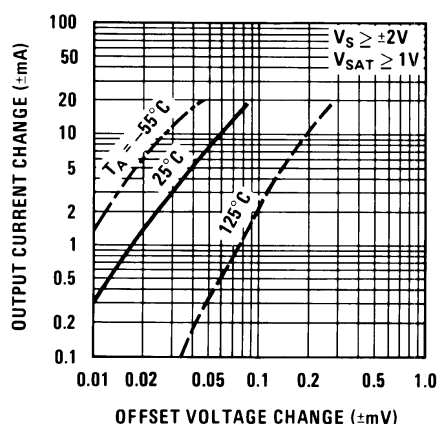


Figure 6. Transconductance

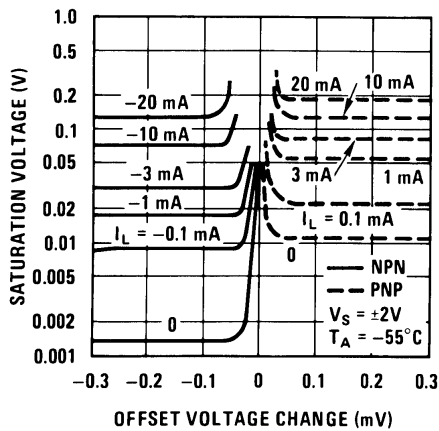
Typical Characteristics (Op Amp) (continued)


Figure 7. Output Saturation Characteristics

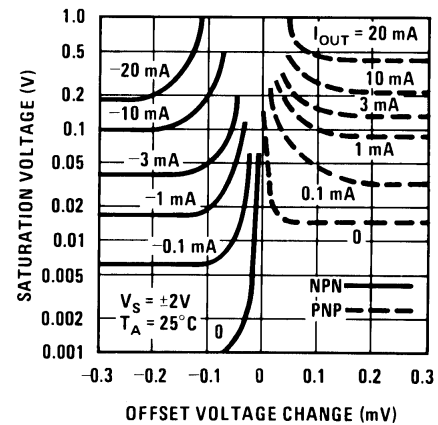


Figure 8. Output Saturation Characteristics

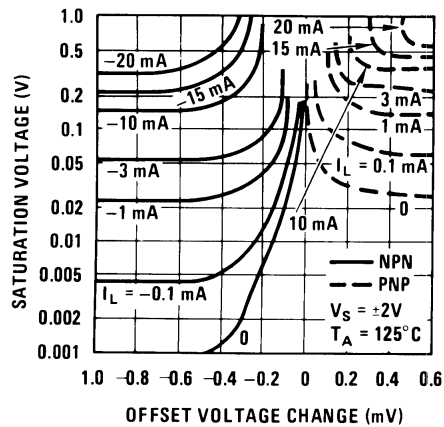


Figure 9. Output Saturation Characteristics

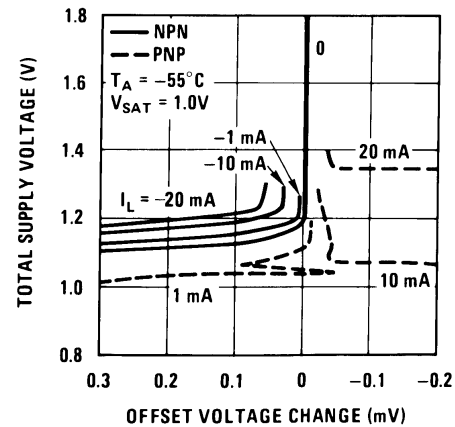


Figure 10. Minimum Supply Voltage

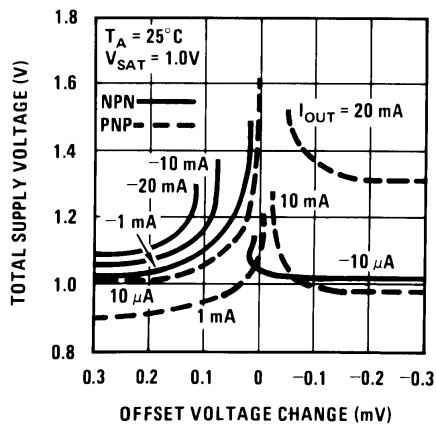


Figure 11. Minimum Supply Voltage

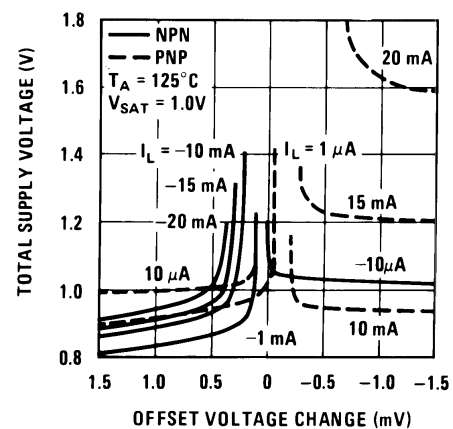


Figure 12. Minimum Supply Voltage

Typical Characteristics (Op Amp) (continued)

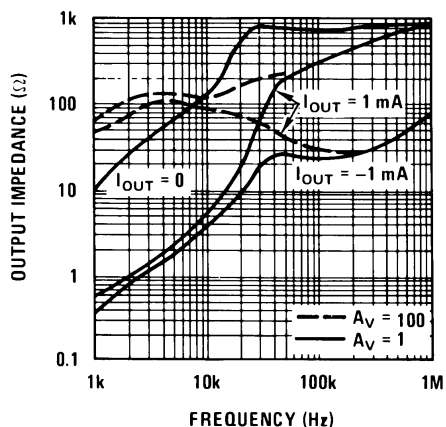


Figure 13. Output Impedance

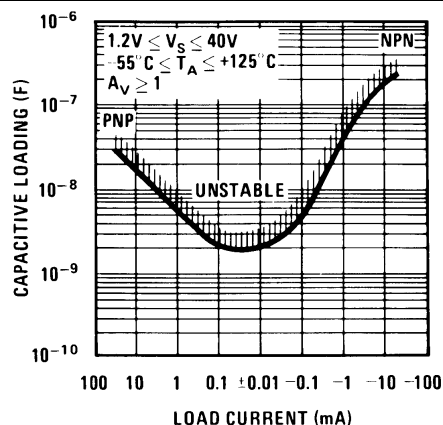


Figure 14. Typical Stability Range

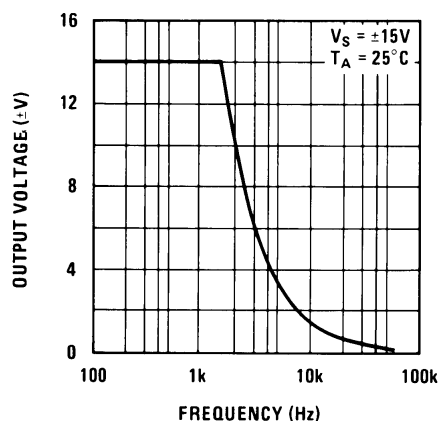


Figure 15. Large Signal Response

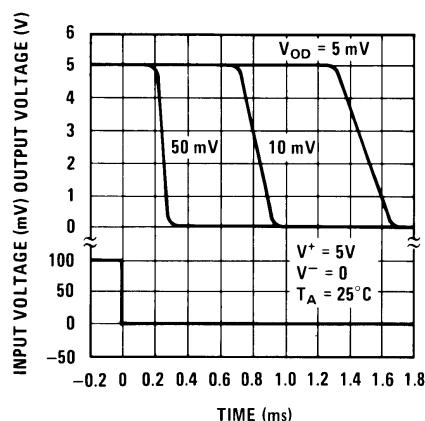


Figure 16. Comparator Response Time For Various Input Overdrives

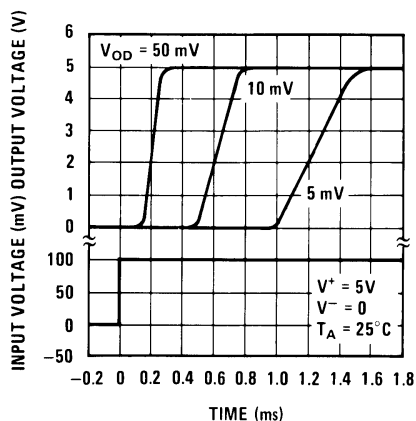


Figure 17. Comparator Response Time For Various Input Overdrives

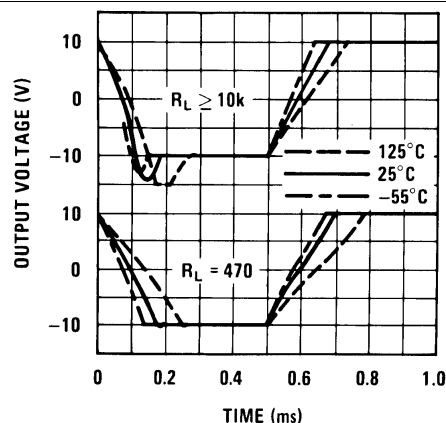


Figure 18. Follower Pulse Response

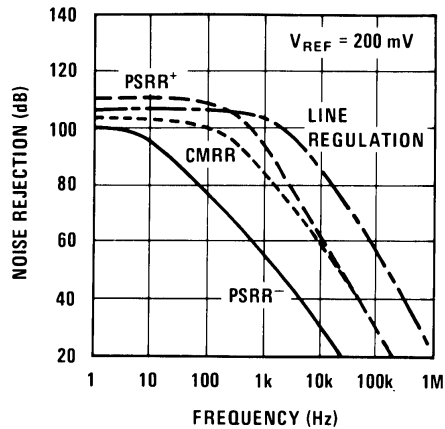
Typical Characteristics (Op Amp) (continued)


Figure 19. Noise Rejection

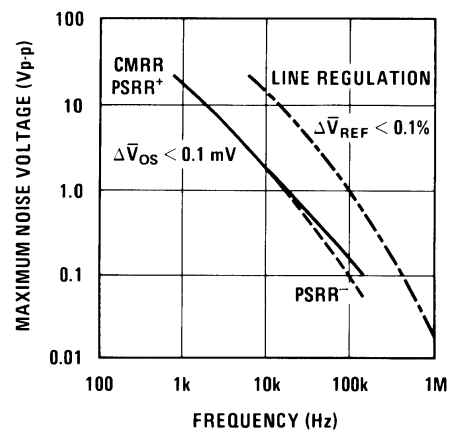


Figure 20. Rejection Slew Limiting

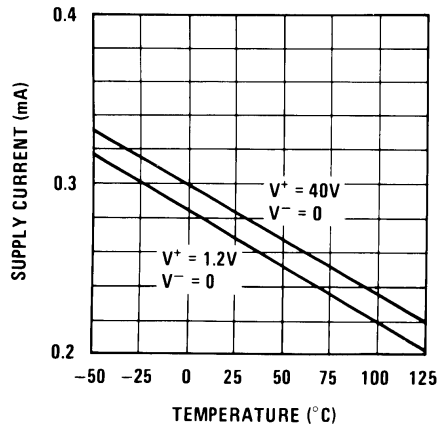


Figure 21. Supply Current

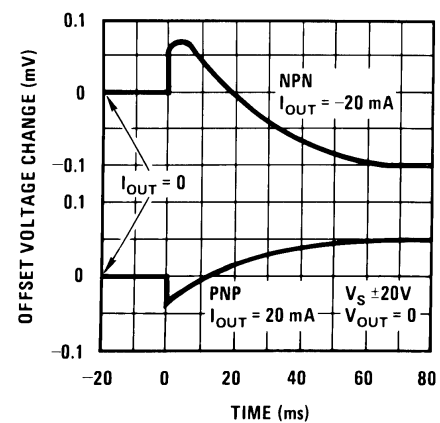


Figure 22. Thermal Gradient Feedback

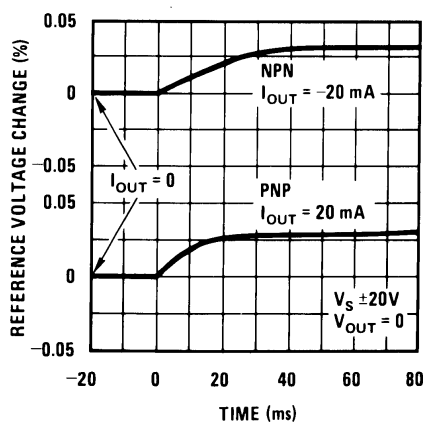


Figure 23. Thermal Gradient Cross-Coupling

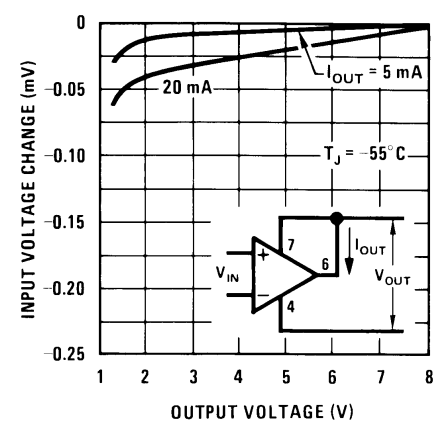


Figure 24. Shunt Gain

Typical Characteristics (Op Amp) (continued)

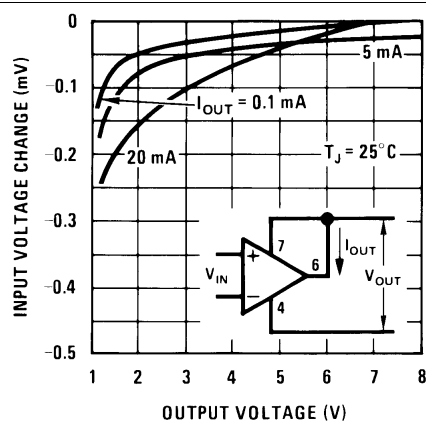


Figure 25. Shunt Gain

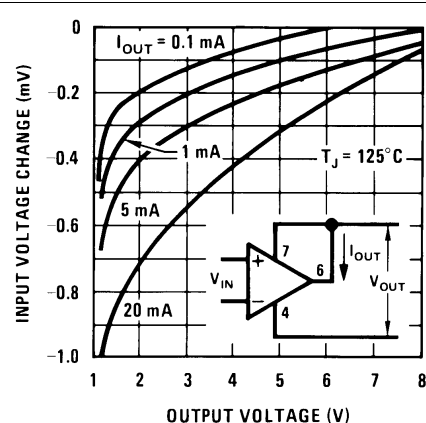


Figure 26. Shunt Gain

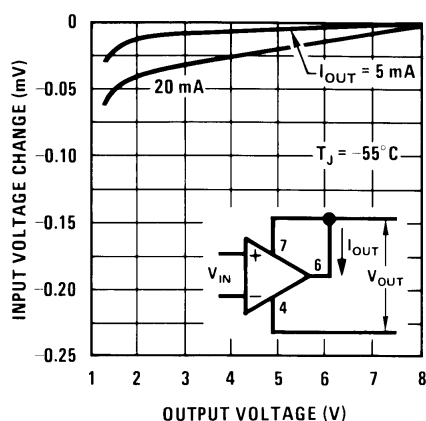


Figure 27. Shunt Gain

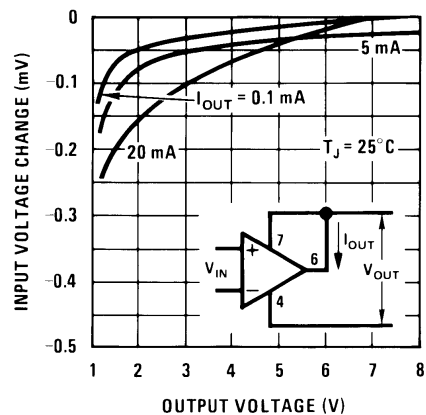


Figure 28. Shunt Gain

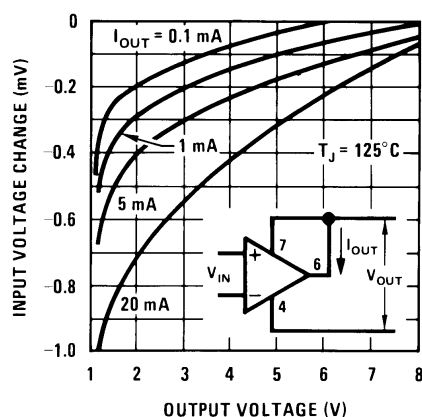


Figure 29. Shunt Gain

6.8.2 Typical Characteristics (Reference)

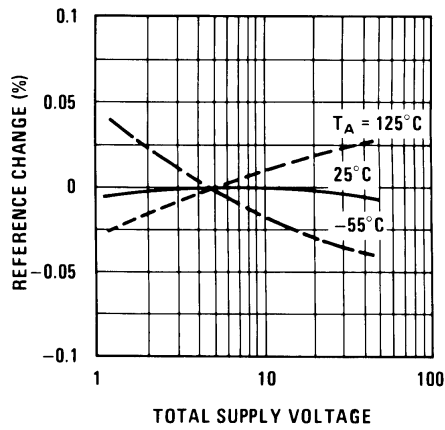


Figure 30. Line Regulation

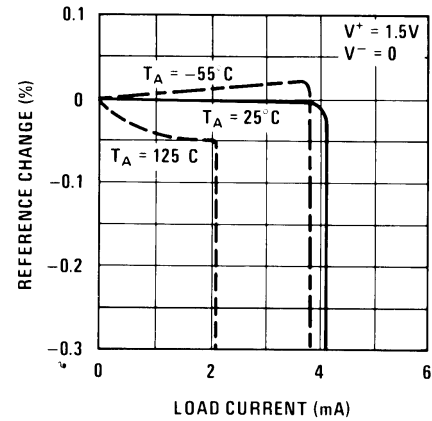


Figure 31. Load Regulation

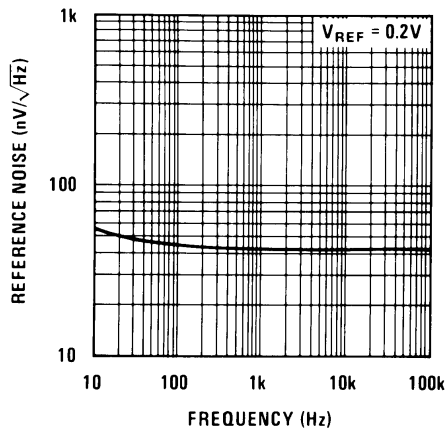


Figure 32. Reference Noise Voltage

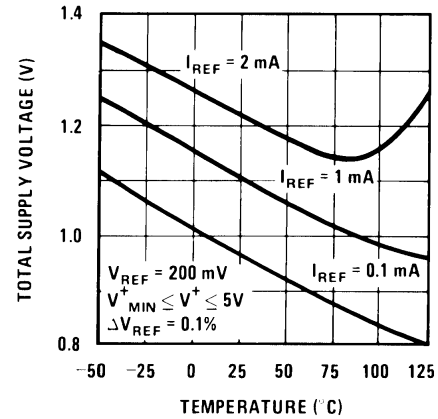


Figure 33. Minimum Supply Voltage

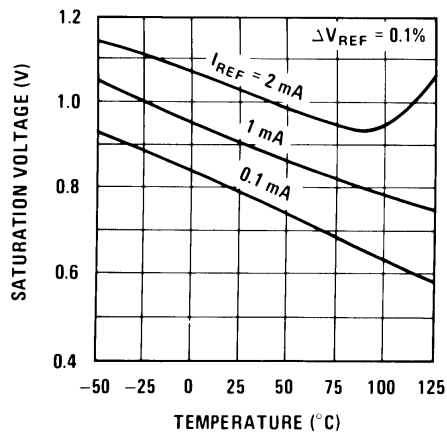


Figure 34. Output Saturation

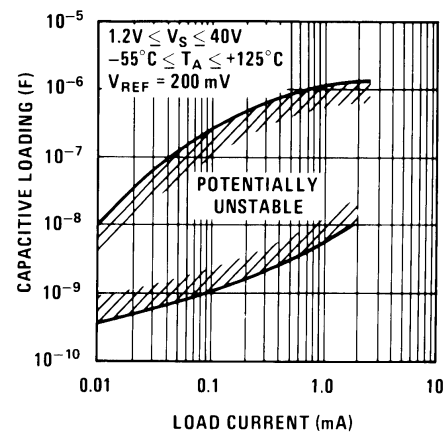


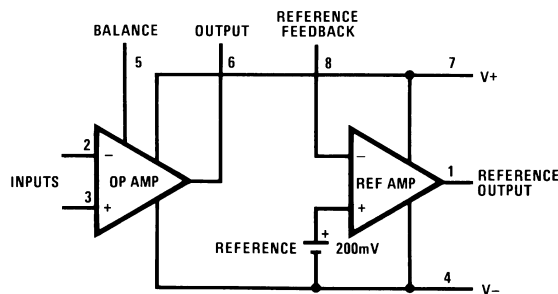
Figure 35. Typical Stability Range

7 Detailed Description

7.1 Overview

The LM10 is a dual-operational amplifier combined with a voltage reference capable of a single-supply operation down to 1.1 V. It provides high overall performance, making it ideal for many general-purpose applications. The circuit can also operate in a floating mode, powered by residual voltage, independent of fixed supplies and it is well-protected from temperature drift.

7.2 Functional Block Diagram



7.3 Feature Description

7.3.1 Operating Characteristics

The LM10 is specified for operation from 1.2 V to 40 V. Many of the specifications apply from -55°C to 125°C . Parameters that can exhibit significant variance with regard to operating voltage or temperature are presented in electrical characteristics tables under [Specifications](#) and in the [Typical Characteristics](#) section.

7.3.2 Common-Mode Voltage Range

The input common-mode voltage range of the LM10 extends from the negative rail to 0.85 V less than the positive rail.

7.3.3 Operational Amplifier

The minimum operating voltage is reduced to nearly one volt and the current gain is less affected by temperature, resulting in a fairly flat bias current over temperature.

7.3.4 Voltage Reference

Second-order nonlinearities are compensated for which eliminates the bowed characteristics of conventional designs, resulting in better temperature stability.

7.4 Device Functional Modes

7.4.1 Floating Mode

To use the device in a floating mode, the operational amplifier output is shorted to V+ which disables the PNP portion of the output stage. Thus, with a positive input signal, neither halves of the output conducts and the current between the supply terminals is equal to the quiescent supply current. With negative input signals, the NPN portion of the output begins to turn on, reaching the short circuit current for a few hundred microvolts overdrive.

7.4.2 Linear Operation

This device can also operate linearly while in the floating mode. An example of this is shown in the [Typical Application](#) section.

8 Application and Implementation

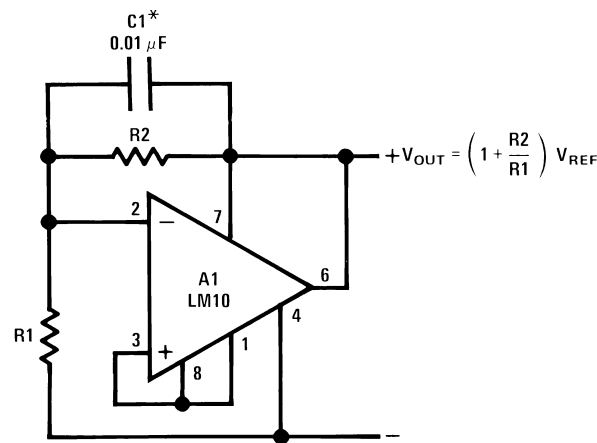
NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

8.1 Application Information

With heavy amplifier loading to V^- , resistance drops in the V^- lead can adversely affect reference regulation. Lead resistance can approach $1\ \Omega$. Therefore, the common to the reference circuitry should be connected as close as possible to the package.

8.2 Typical Application



* required for capacitive loading

Figure 36. Shunt Voltage Regulator

8.2.1 Design Requirements

Table 1 lists the design parameters for this example.

Table 1. Design Parameters

DESIGN PARAMETERS	EXAMPLE VALUE
Ambient Temperature Range	–55°C to 125°C
Supply Voltage Range	1.2 V to 40 V
Common-Mode Input Range	(V^-) to (V^+) – 0.85 V

8.2.2 Detailed Design Procedure

Given that the transfer function of this circuit is:

$$V_{OUT} = \left(1 + \frac{R_2}{R_1}\right) V_{REF} \quad (1)$$

the output can be set between 0.2 V and the breakdown voltage of the IC by selecting an appropriate value for R_2 . The circuit regulates for input voltages within a saturation drop of the output (typically 0.4 V at 20 mA and 0.15 V at 5 mA). The regulator is protected from shorts or overloads by current limiting and thermal shutdown.

Typical regulation is about 0.05% load and 0.003%/V line. A substantial improvement in regulation can be effected by connecting the operational amplifier as a follower and setting the reference to the desired output voltage. This has the disadvantage that the minimum input-output differential is increased to a little more than a diode drop. If the operational amplifier were connected for a gain of 2, the output could again saturate. But this requires an additional pair of precision resistors.

The regulator in [Figure 36](#) could be made adjustable to zero by connecting the operational amplifier to a potentiometer on the reference output. This has the disadvantage that the regulation at the lower voltage settings is not as good as it might otherwise be.

8.2.3 Application Curve

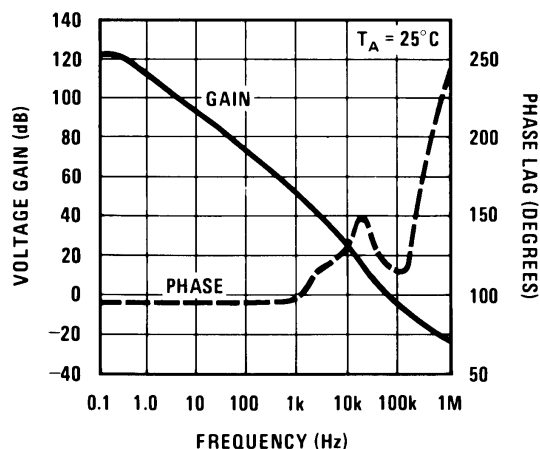


Figure 37. Frequency Response

8.3 System Examples

Circuit descriptions available in application note AN-211 ([SNOA638](#)).

8.3.1 Operational Amplifier Offset Adjustment

(Pin numbers are for 8-pin packages)

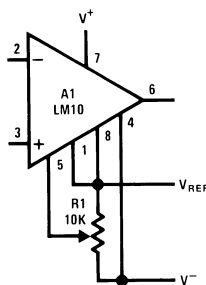


Figure 38. Standard

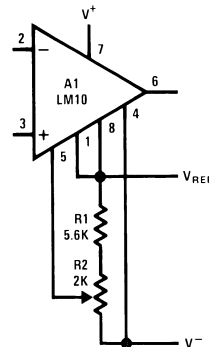


Figure 39. Limited Range

System Examples (continued)

(Pin numbers are for 8-pin packages)

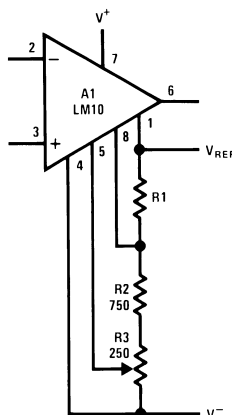


Figure 40. Limited Range With Boosted Reference

8.3.2 Positive Regulators

(Pin numbers are for 8-pin packages)

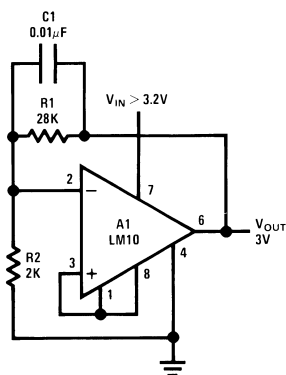


Figure 41. Low Voltage

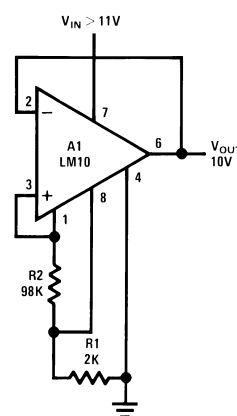
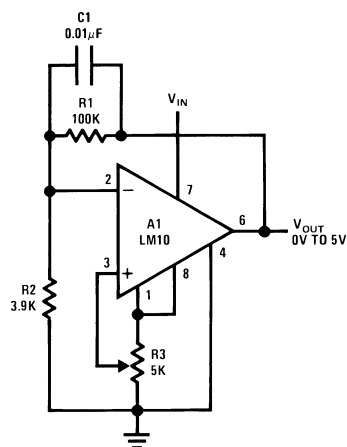


Figure 42. Best Regulation



Use only electrolytic output capacitors.

Figure 43. Zero Output

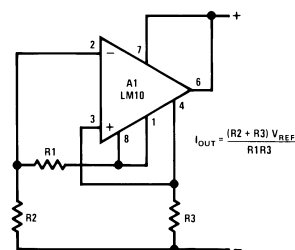
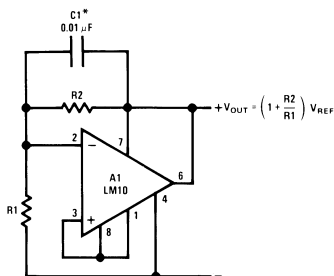


Figure 44. Current Regulator

System Examples (continued)

(Pin numbers are for 8-pin packages)



Required For Capacitive Loading

Figure 45. Shunt Regulator

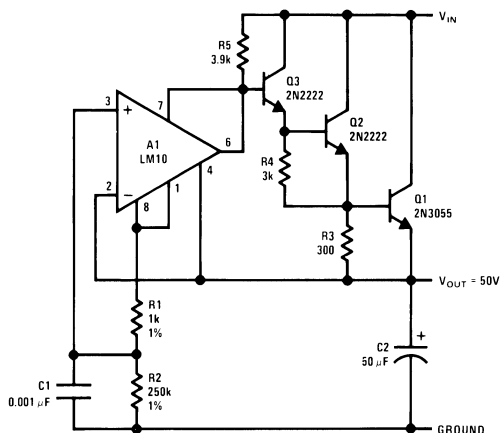
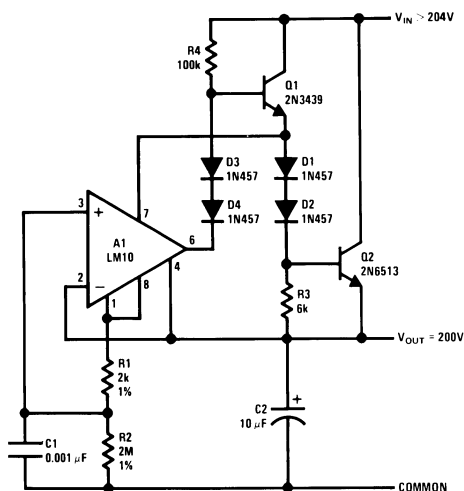
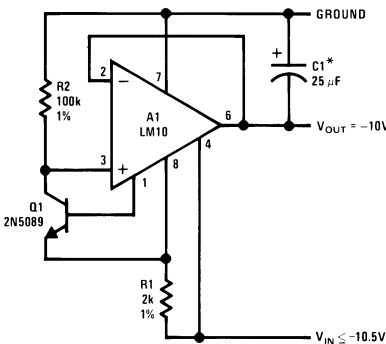


Figure 47. Precision Regulator



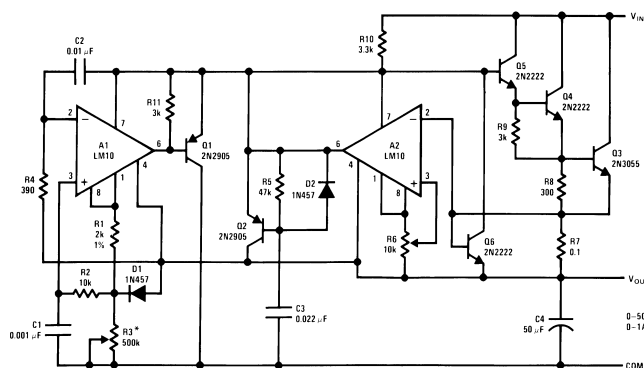
$$V_{OUT} = \frac{R_2}{R_1} V_{REF}$$

Figure 49. HV Regulator



*Electrolytic

Figure 46. Negative Regulator



$$*V_{OUT} = 10^{-4} R_3$$

Figure 48. Laboratory Power Supply

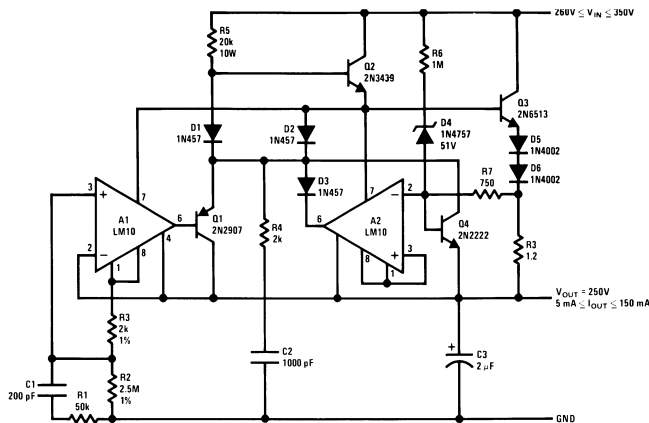


Figure 50. Protected HV Regulator

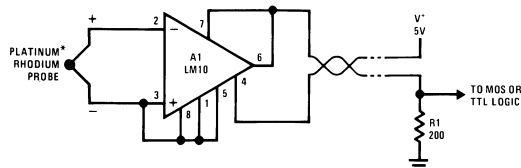
LM10

SNOSBH4E – MAY 1998 – REVISED OCTOBER 2015

www.ti.com

System Examples (continued)

(Pin numbers are for 8-pin packages)



*800°C Threshold Is Established By Connecting Balance To V_{REF} .

Figure 51. Flame Detector

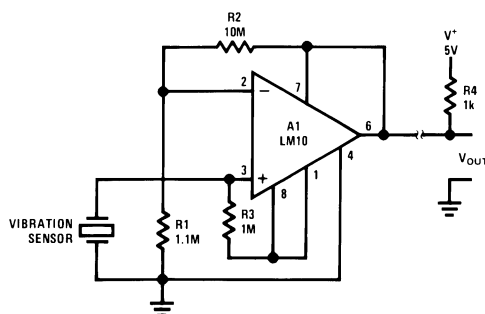


Figure 53. Remote Amplifier

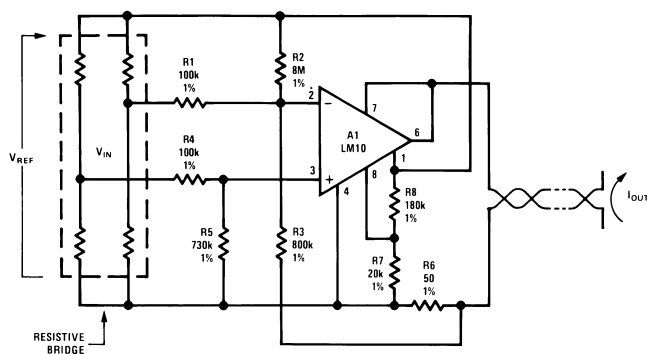
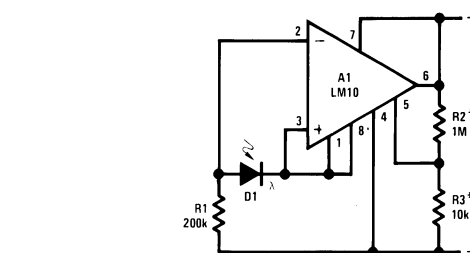


Figure 55. Transmitter for Bridge Sensor



*Provides Hysteresis

Figure 52. Light Level Sensor

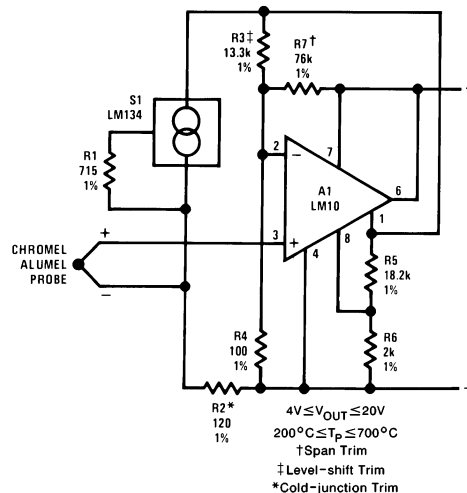
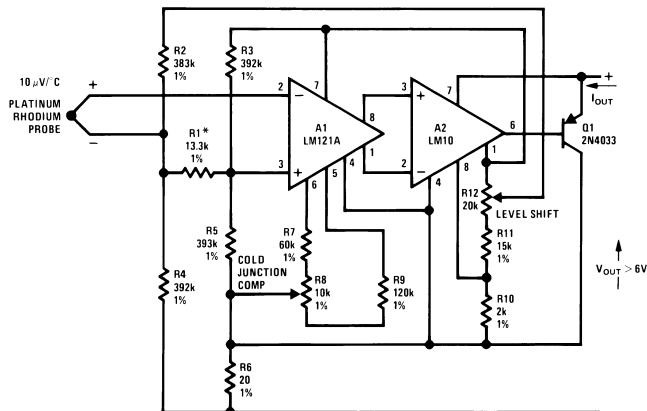


Figure 54. Remote Thermocouple Amplifier

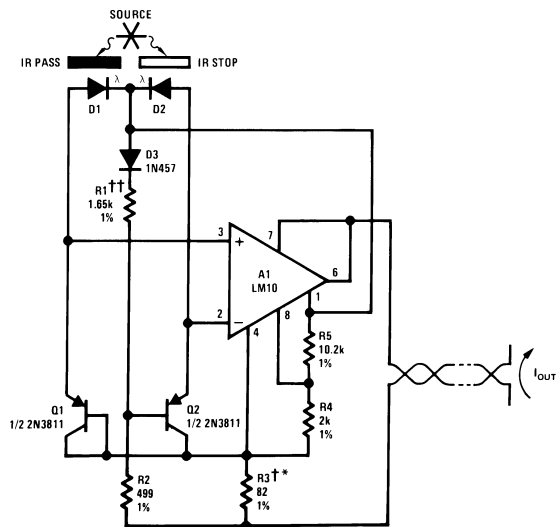
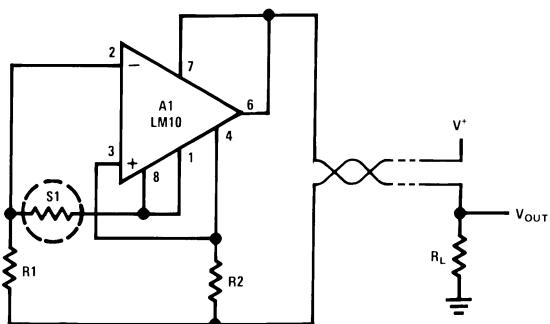


10 mA ≤ I_{OUT} ≤ 50 mA
500°C ≤ T_P ≤ 1500°C
*Gain Trim

Figure 56. Precision Thermocouple Transmitter

System Examples (continued)

(Pin numbers are for 8-pin packages)



††Level-shift Trim

*Scale Factor Trim

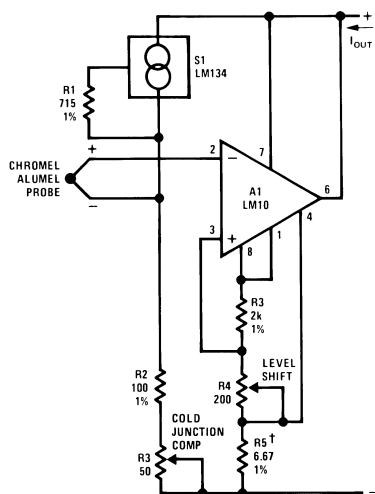
†Copper Wire Wound

$1 \text{ mA} \leq I_{OUT} \leq 5 \text{ mA}$

$0.01 \leq \frac{I_{D2}}{I_{D1}} \leq 100$

Figure 57. Resistance Thermometer Transmitter

Figure 58. Optical Pyrometer

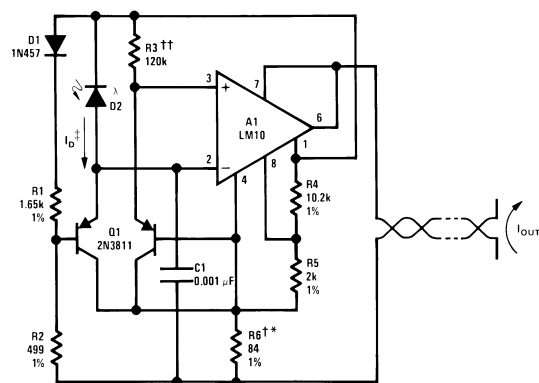


$200^{\circ}\text{C} \leq T_P \leq 700^{\circ}\text{C}$

$1 \text{ mA} \leq I_{OUT} \leq 5 \text{ mA}$

†Gain Trim

Figure 59. Thermocouple Transmitter



$1 \text{ mA} \leq I_{OUT} \leq 5 \text{ mA}$

$\pm 50 \mu\text{A} \leq I_D \leq 500 \mu\text{A}$

††Center Scale Trim

†Scale Factor Trim

*Copper Wire Wound

Figure 60. Logarithmic Light Sensor

System Examples (continued)

(Pin numbers are for 8-pin packages)

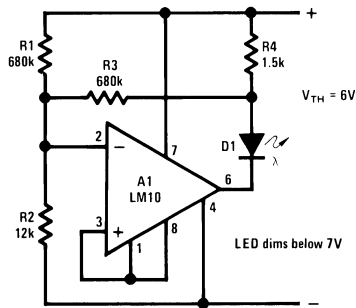


Figure 61. Battery-level Indicator

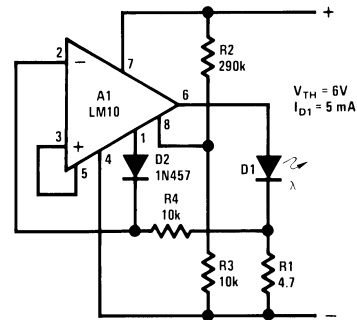
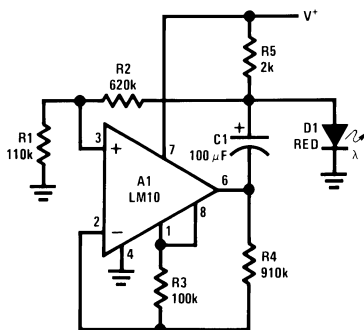
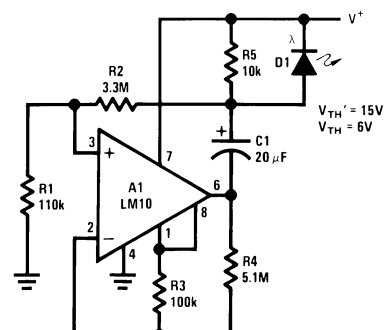


Figure 62. Battery-threshold Indicator



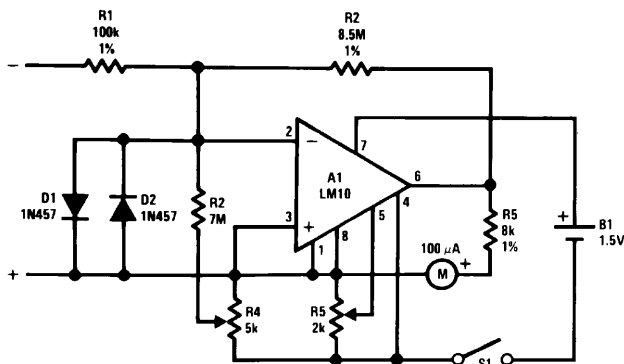
Flashes Above 1.2V
Rate Increases With
Voltage

Figure 63. Single-cell Voltage Monitor



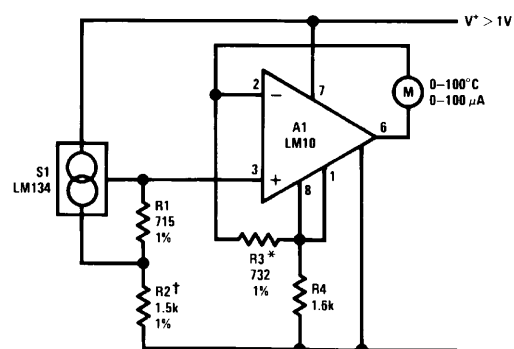
Flash Rate Increases
Above 6V and Below 15V

Figure 64. Double-ended Voltage Monitor



INPUT
10 mV, 100nA
FULL-SCALE

Figure 65. Meter Amplifier



*Trim For Span
†Trim For Zero

Figure 66. Thermometer

(Pin numbers are for 8-pin packages)

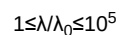


Figure 67. Light Meter

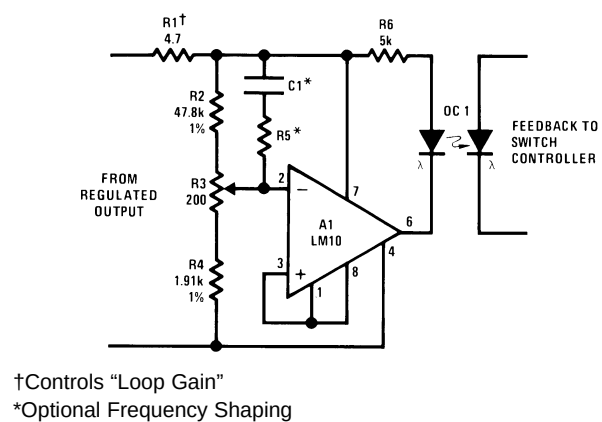
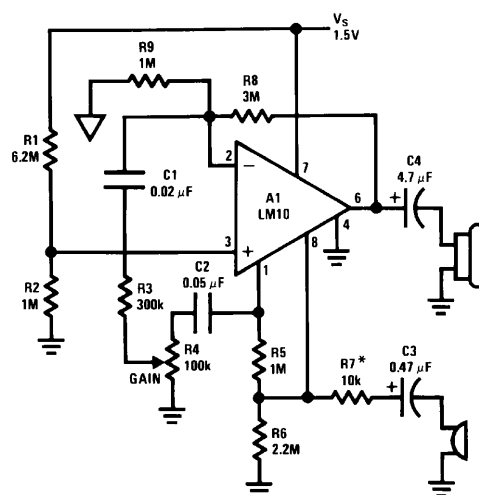


Figure 69. Isolated Voltage Sensor



$Z_{OUT} \sim 680\Omega @ 5 \text{ kHz}$
 $A_V \leq 1k$
 $f_1 \sim 100 \text{ Hz}$
 $f_2 \sim 5 \text{ kHz}$
 $R_L \sim 500$
 *Max Gain Trim

Figure 68. Microphone Amplifier

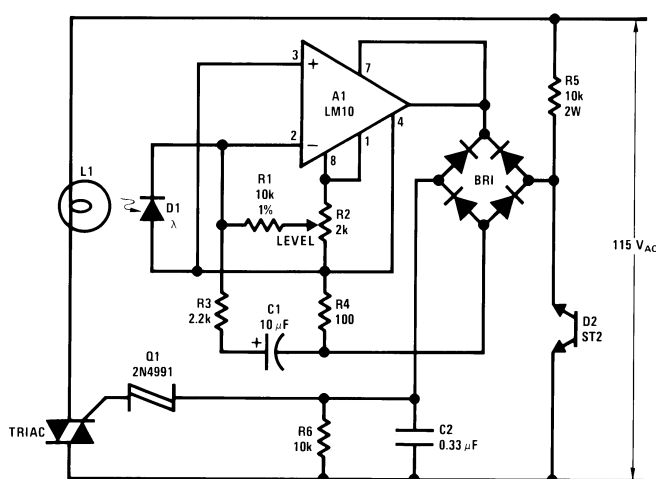


Figure 70. Light-Level Controller

System Examples (continued)

(Pin numbers are for 8-pin packages)

8.3.3 Reference and Internal Regulator

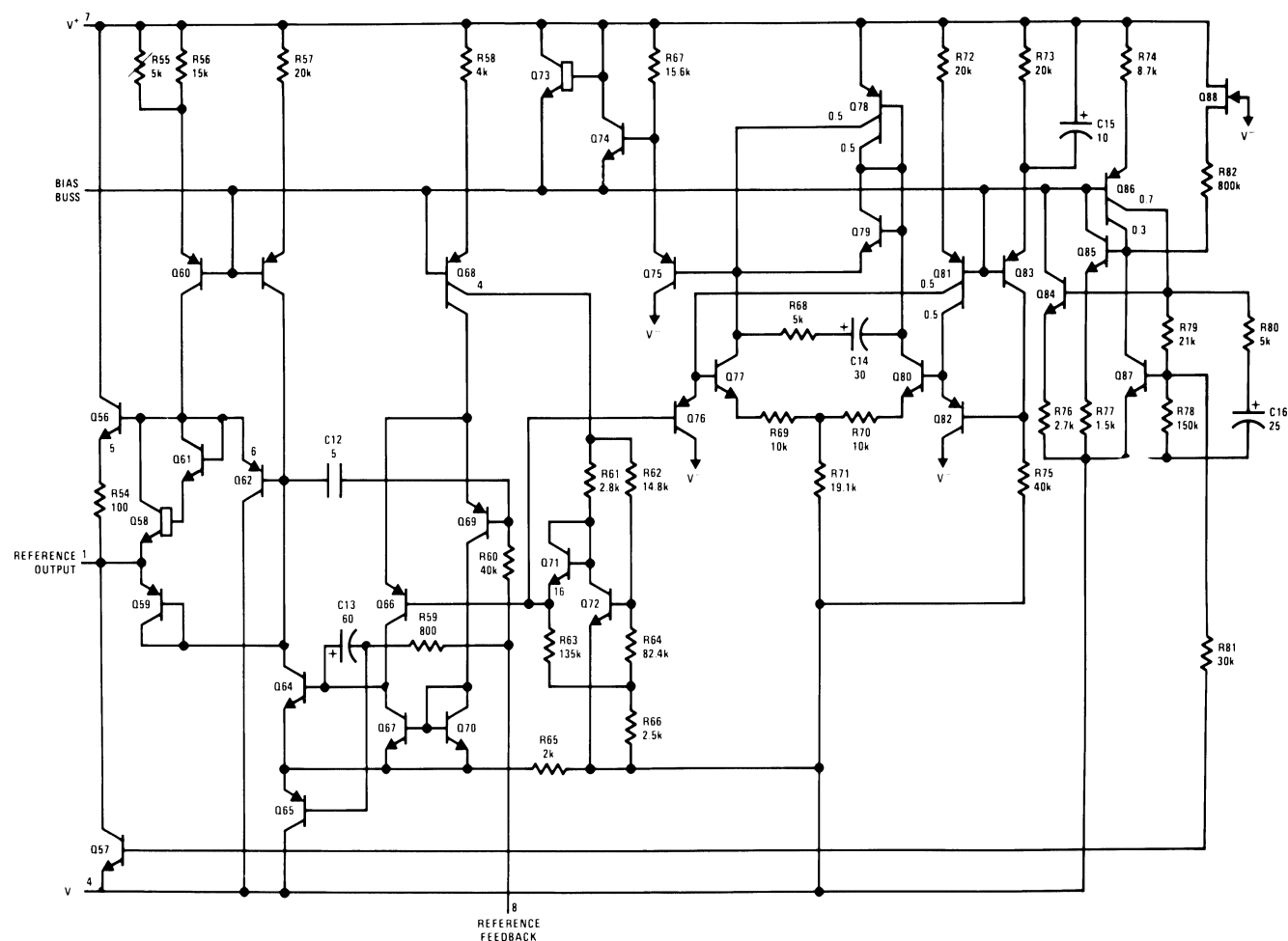


Figure 71. Reference and Internal Regulator

9 Power Supply Recommendations

The LM10 is specified for operation from 1.2 V to 40 V unless otherwise stated. Many specifications apply from –55°C to 125°C. Parameters that can exhibit significant variance with regard to operating voltage or temperature are presented in the [Specifications](#) section.

CAUTION

Supply voltages larger than 40 V can permanently damage the device; see the [Absolute Maximum Ratings](#) table.

10 Layout

10.1 Layout Guidelines

For best operational performance of the device, good printed-circuit board (PCB) layout practices are recommended. Low-loss, 0.1- μ F bypass capacitors should be connected between each supply pin and ground, placed as close to the device as possible. A single bypass capacitor from V+ to ground is applicable to single-supply applications.

10.2 Layout Example

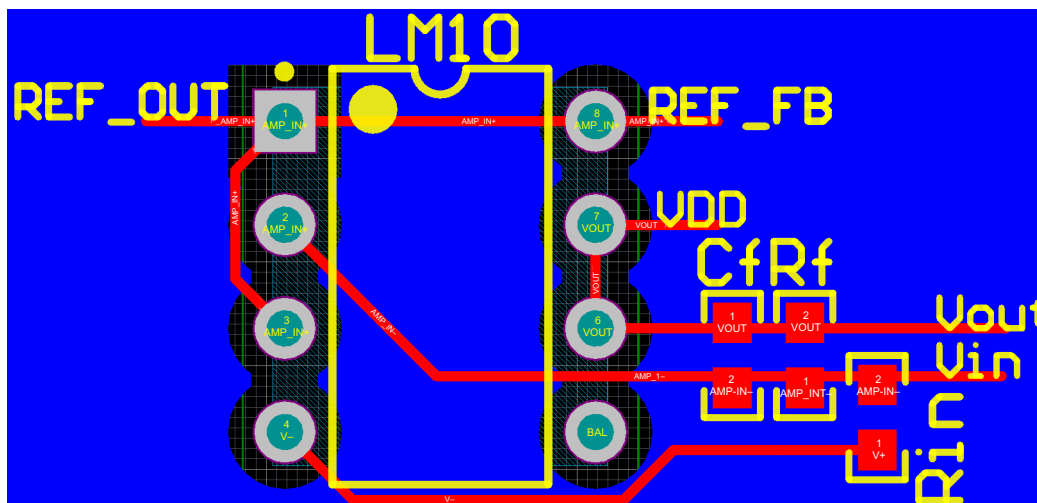


Figure 72. Layout Example

11 Device and Documentation Support

11.1 Device Support

11.1.1 Device Nomenclature

11.1.1.1 Definition of Terms

Input offset voltage: That voltage which must be applied between the input terminals to bias the unloaded output in the linear region.

Input offset current: The difference in the currents at the input terminals when the unloaded output is in the linear region.

Input bias current: The absolute value of the average of the two input currents.

Input resistance: The ratio of the change in input voltage to the change in input current on either input with the other grounded.

Large signal voltage gain: The ratio of the specified output voltage swing to the change in differential input voltage required to produce it.

Shunt gain: The ratio of the specified output voltage swing to the change in differential input voltage required to produce it with the output tied to the V^+ terminal of the IC. The load and power source are connected between the V^+ and V^- terminals, and input common-mode is referred to the V^- terminal.

Common-mode rejection: The ratio of the input voltage range to the change in offset voltage between the extremes.

Supply-voltage rejection: The ratio of the specified supply-voltage change to the change in offset voltage between the extremes.

Line regulation: The average change in reference output voltage over the specified supply voltage range.

Load regulation: The change in reference output voltage from no load to that load specified.

Feedback sense voltage: The voltage, referred to V^- , on the reference feedback terminal while operating in regulation.

Reference amplifier gain: The ratio of the specified reference output change to the change in feedback sense voltage required to produce it.

Feedback current: The absolute value of the current at the feedback terminal when operating in regulation.

Supply current: The current required from the power source to operate the amplifier and reference with their outputs unloaded and operating in the linear range.

11.2 Documentation Support

11.2.1 Related Documentation

For related documentation, see the following:

AN-211 New Op Amp Ideas, [SNOA638](#)

11.3 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's [Terms of Use](#).

TI E2E™ Online Community *TI's Engineer-to-Engineer (E2E) Community*. Created to foster collaboration among engineers. At [e2e.ti.com](#), you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

11.4 Trademarks

E2E is a trademark of Texas Instruments.
All other trademarks are the property of their respective owners.

11.5 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

11.6 Glossary

[SLYZ022](#) — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

12 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
LM10BH	Active	Production	TO-CAN (LMG) 8	500 TRAY NON-STD	No	Call TI	Level-1-NA-UNLIM	-40 to 85	(LM10BH, LM10BH)
LM10BH/NOPB	Active	Production	TO-CAN (LMG) 8	500 TRAY NON-STD	Yes	Call TI	Level-1-NA-UNLIM	-40 to 85	(LM10BH, LM10BH)
LM10CH	Active	Production	TO-CAN (LMG) 8	500 TRAY NON-STD	No	Call TI	Level-1-NA-UNLIM	0 to 70	(LM10CH, LM10CH)
LM10CH/NOPB	Active	Production	TO-CAN (LMG) 8	500 OTHER	Yes	Call TI	Level-1-NA-UNLIM	0 to 70	(LM10CH, LM10CH)
LM10CLN/NOPB	Active	Production	PDIP (P) 8	40 TUBE	Yes	NIPDAU	Level-1-NA-UNLIM	0 to 70	LM10CLN
LM10CLN/NOPB.B	Active	Production	PDIP (P) 8	40 TUBE	Yes	NIPDAU	Level-1-NA-UNLIM	0 to 70	LM10CLN
LM10CN/NOPB	Active	Production	PDIP (P) 8	40 TUBE	Yes	NIPDAU	Level-1-NA-UNLIM	0 to 70	LM 10CN
LM10CN/NOPB.B	Active	Production	PDIP (P) 8	40 TUBE	Yes	NIPDAU	Level-1-NA-UNLIM	0 to 70	LM 10CN
LM10CWM/NOPB	Active	Production	SOIC (NPA) 14	50 TUBE	Yes	SN	Level-3-260C-168 HR	0 to 70	LM10CWM
LM10CWM/NOPB.B	Active	Production	SOIC (NPA) 14	50 TUBE	Yes	SN	Level-3-260C-168 HR	0 to 70	LM10CWM
LM10CWMX/NOPB	Active	Production	SOIC (NPA) 14	1000 LARGE T&R	Yes	SN	Level-3-260C-168 HR	0 to 70	LM10CWM
LM10CWMX/NOPB.B	Active	Production	SOIC (NPA) 14	1000 LARGE T&R	Yes	SN	Level-3-260C-168 HR	0 to 70	LM10CWM

⁽¹⁾ **Status:** For more details on status, see our [product life cycle](#).

⁽²⁾ **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

⁽⁴⁾ **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

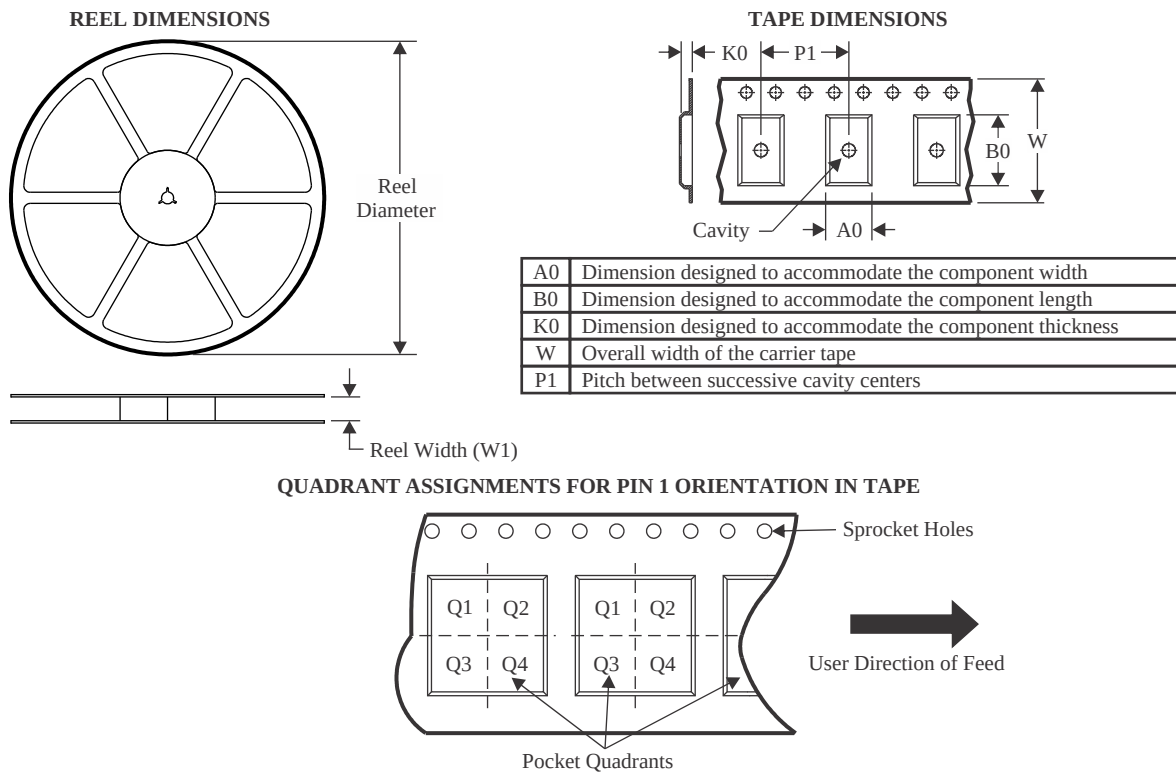
⁽⁶⁾ **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

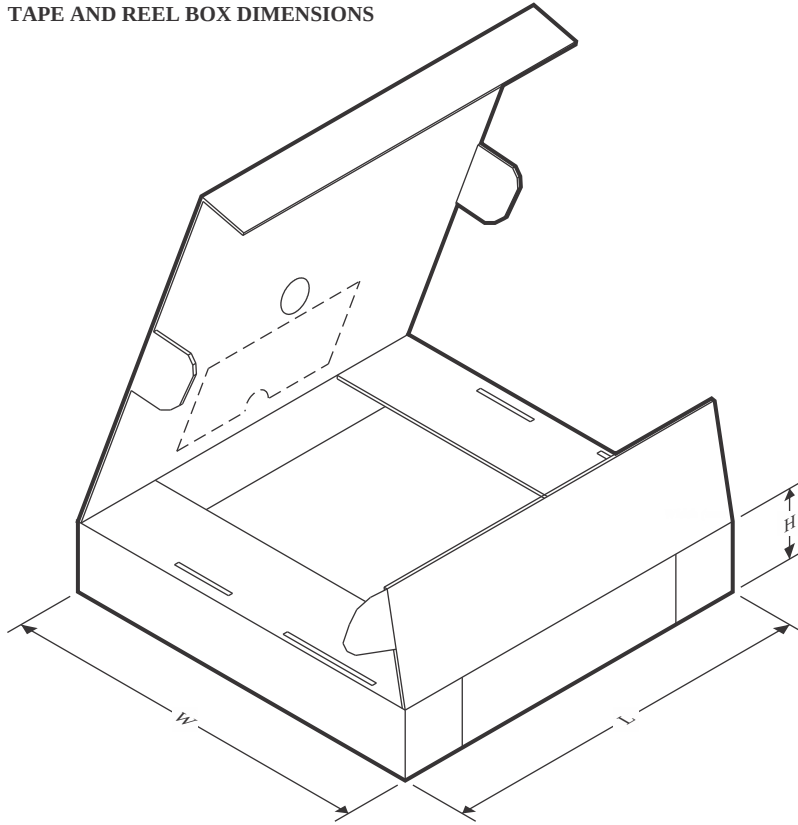
TAPE AND REEL INFORMATION



*All dimensions are nominal

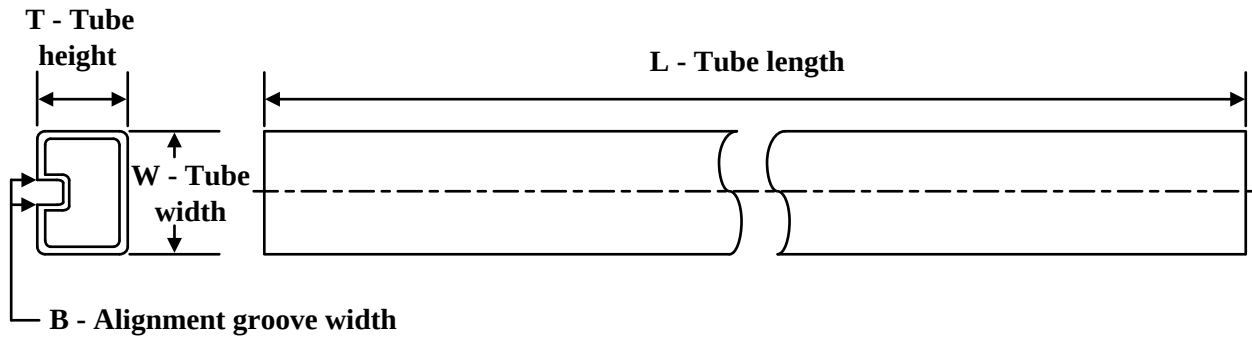
Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
LM10CWMX/NOPB	SOIC	NPA	14	1000	330.0	16.4	10.9	9.5	3.2	12.0	16.0	Q1

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

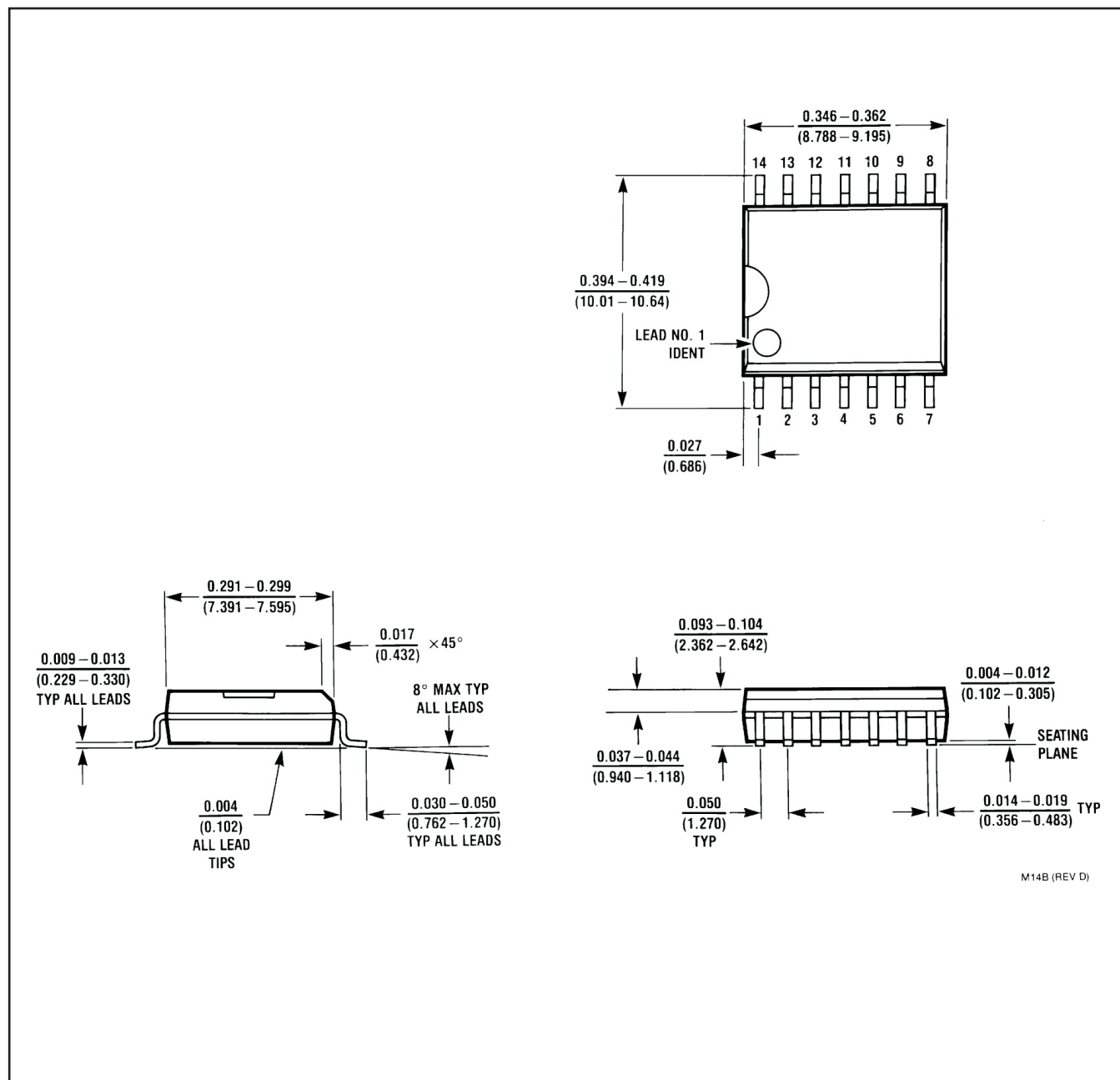
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
LM10CWMX/NOPB	SOIC	NPA	14	1000	356.0	356.0	36.0

TUBE


*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (μm)	B (mm)
LM10CLN/NOPB	P	PDIP	8	40	502	14	11938	4.32
LM10CLN/NOPB.B	P	PDIP	8	40	502	14	11938	4.32
LM10CN/NOPB	P	PDIP	8	40	502	14	11938	4.32
LM10CN/NOPB.B	P	PDIP	8	40	502	14	11938	4.32
LM10CWM/NOPB	NPA	SOIC	14	50	495	15	5842	7.87
LM10CWM/NOPB.B	NPA	SOIC	14	50	495	15	5842	7.87

NPA0014B

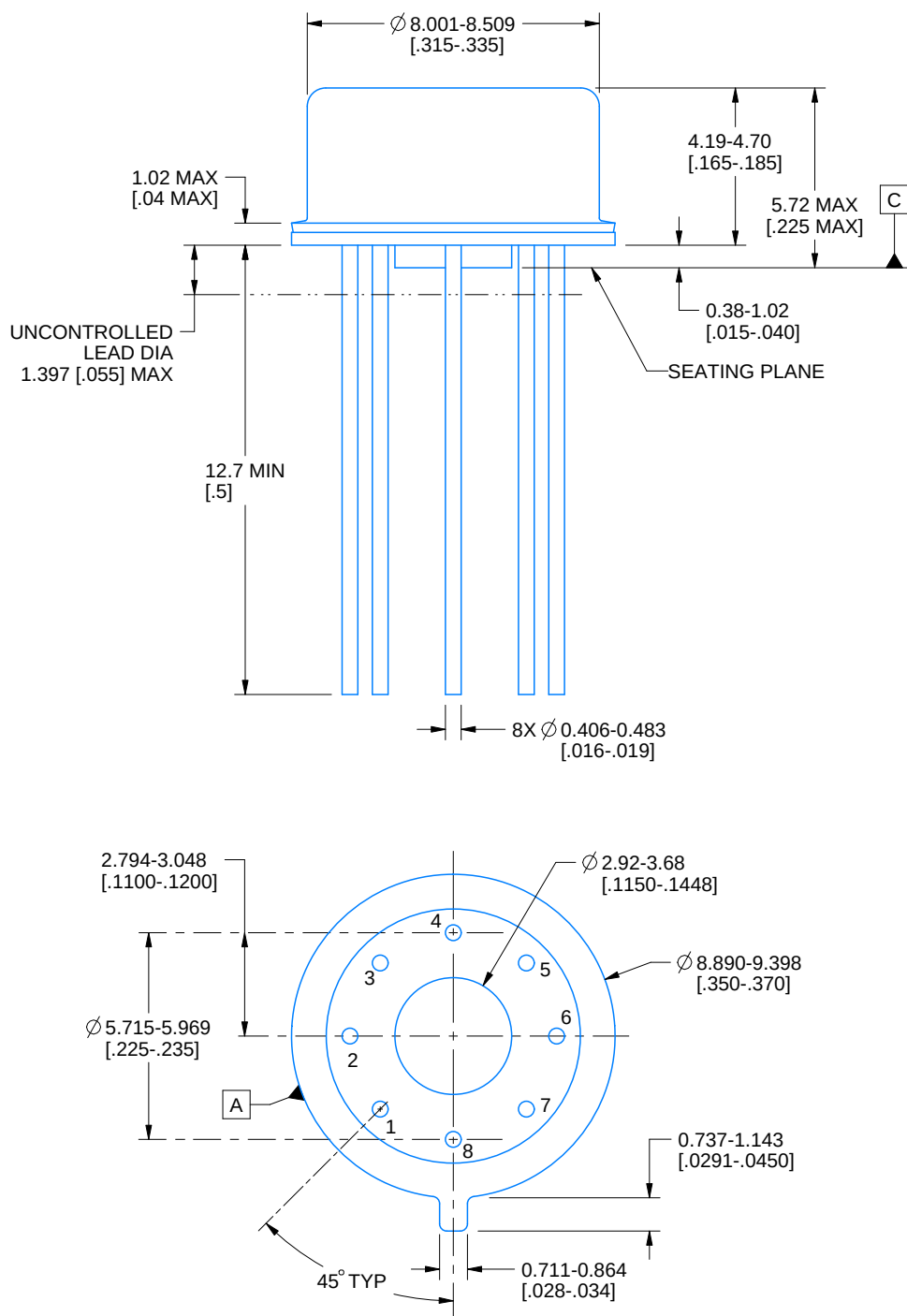


PACKAGE OUTLINE

LMG0008A

TO-CAN - 5.72 mm max height

TRANSISTOR OUTLINE



4224369/C 09/2024

NOTES:

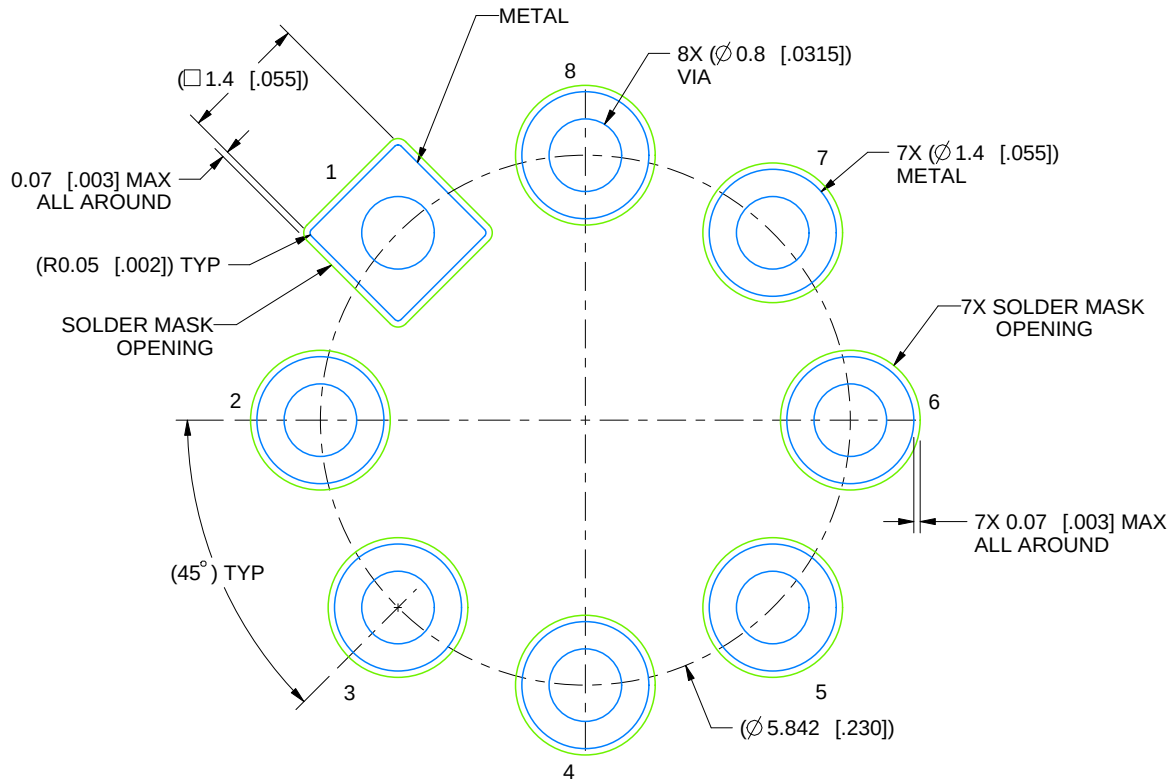
1. All linear dimensions are in millimeters [inches]. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.

EXAMPLE BOARD LAYOUT

LMG0008A

TO-CAN - 5.72 mm max height

TRANSISTOR OUTLINE

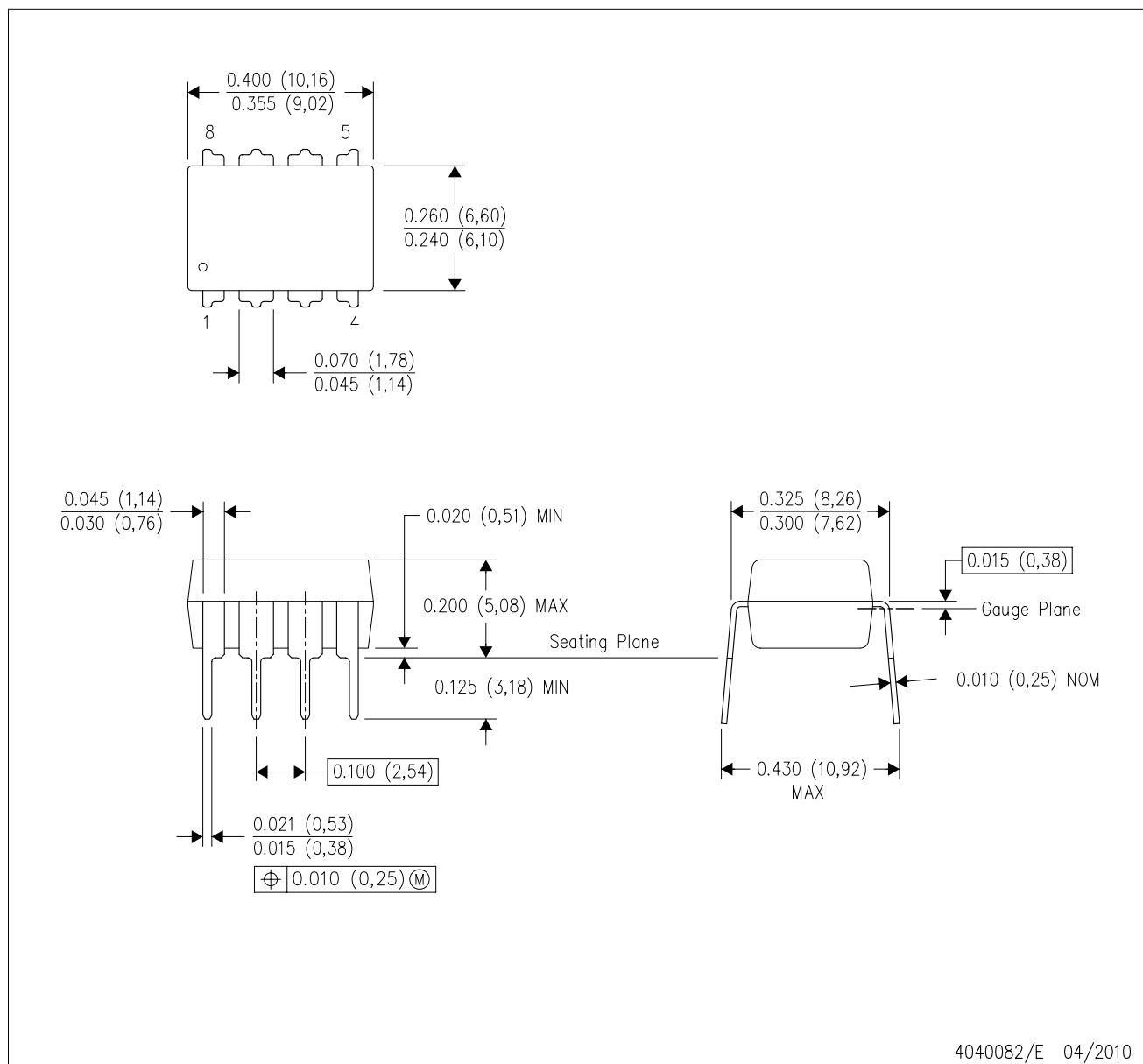


LAND PATTERN EXAMPLE
NON-SOLDER MASK DEFINED
SCALE: 12X

4224369/C 09/2024

P (R-PDIP-T8)

PLASTIC DUAL-IN-LINE PACKAGE



- NOTES:
- A. All linear dimensions are in inches (millimeters).
 - B. This drawing is subject to change without notice.
 - C. Falls within JEDEC MS-001 variation BA.

IMPORTANT NOTICE AND DISCLAIMER

TI PROVIDES TECHNICAL AND RELIABILITY DATA (INCLUDING DATA SHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, SAFETY INFORMATION, AND OTHER RESOURCES "AS IS" AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS AND IMPLIED, INCLUDING WITHOUT LIMITATION ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for skilled developers designing with TI products. You are solely responsible for (1) selecting the appropriate TI products for your application, (2) designing, validating and testing your application, and (3) ensuring your application meets applicable standards, and any other safety, security, regulatory or other requirements.

These resources are subject to change without notice. TI grants you permission to use these resources only for development of an application that uses the TI products described in the resource. Other reproduction and display of these resources is prohibited. No license is granted to any other TI intellectual property right or to any third party intellectual property right. TI disclaims responsibility for, and you will fully indemnify TI and its representatives against, any claims, damages, costs, losses, and liabilities arising out of your use of these resources.

TI's products are provided subject to [TI's Terms of Sale](#) or other applicable terms available either on [ti.com](https://www.ti.com) or provided in conjunction with such TI products. TI's provision of these resources does not expand or otherwise alter TI's applicable warranties or warranty disclaimers for TI products.

TI objects to and rejects any additional or different terms you may have proposed.

Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265
Copyright © 2025, Texas Instruments Incorporated